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## Tunable top-down fabrication and functional surface coating of single-crystal titanium dioxide nanostructures and nanoparticles†

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Titanium dioxide (TiO<sub>2</sub>) is a key component of diverse optical and electronic applications that exploit its exceptional material properties. In particular, the use of TiO<sub>2</sub> in its single-crystalline phase can offer substantial advantages over its amorphous and polycrystalline phases for existing and yet-to-be-developed applications. However, the implementation of single-crystal TiO<sub>2</sub> has been hampered by challenges in its fabrication and subsequent surface functionalization. Here, we introduce a novel top-down approach that allows for batch fabrication of uniform high-aspect-ratio single-crystal TiO<sub>2</sub> nanostructures with targeted sidewall profiles. We complement our fabrication approach with a functionalization strategy that achieves dense, uniform, and area-selective coating with a variety of biomolecules. This allows us to fabricate single-crystal rutile TiO<sub>2</sub> nanocylinders tethered with individual DNA molecules for use as force- and torque-transducers in an optical torque wrench. These developments provide the means for increased exploitation of the superior material properties of single-crystal TiO<sub>2</sub> at the nanoscale.

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### Introduction

Micro- and nanostructures based on titanium dioxide (TiO<sub>2</sub>) have been utilized in numerous applications that exploit the unique properties of this material (Fig. S1†). For example, the high photocatalytic activity of TiO<sub>2</sub> is used for water splitting<sup>1</sup> and air purification.<sup>2</sup> The electrical properties of TiO<sub>2</sub>, which include a tunable resistance, a high dielectric constant, carrier transport abilities, and a wide band gap, render it a preferred material for sensors,<sup>3</sup> memory devices,<sup>4</sup> transistors,<sup>5</sup> solar cells,<sup>6</sup> and batteries.<sup>7,8</sup> Furthermore, the optical properties of TiO<sub>2</sub>, *e.g.* high refractive index and optical nonlinearity, make

it find use in optical waveguides,<sup>9</sup> photonic crystals,<sup>10</sup> and optical trapping.<sup>11</sup>

In particular, the use of TiO<sub>2</sub> in its single-crystalline phase can offer substantial advantages over its amorphous and polycrystalline phases for existing and new applications. For instance, single-crystal TiO<sub>2</sub> allows improved control of surface properties, *e.g.* photochemical reactivity<sup>12</sup> and surface wettability,<sup>13</sup> by making use of the different crystallographic orientations. The higher carrier mobility of single-crystal TiO<sub>2</sub> renders it a promising material for transistors and (bio)sensors<sup>14</sup> and may enhance the efficiency of dye-sensitized solar cells.<sup>15</sup> Furthermore, optical waveguides and photonic crystals composed of single-crystal TiO<sub>2</sub><sup>16,17</sup> are expected, due to their highly ordered atomic structures, to exhibit improved light transmission and nonlinear responses.<sup>18,19</sup> Lastly, the single-crystal rutile polymorph of TiO<sub>2</sub> has an exceptionally large optical birefringence, which makes it an excellent candidate for incorporation into torque transducers for *e.g.* single-molecule spectroscopy.<sup>20</sup>

To facilitate the application of TiO<sub>2</sub> in its single-crystalline phase, major challenges in both fabrication and surface functionalization must be addressed. First, it is important to control structural parameters such as feature size, shape, and pitch that determine the resulting physical responses of fabricated TiO<sub>2</sub> nanostructures. Such physical responses impact *e.g.* gas sensing performance,<sup>3</sup> light scattering efficiency,<sup>6</sup> light propagation behavior,<sup>9</sup> and optical trapping capabilities.<sup>11</sup>

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† Electronic supplementary information (ESI) available: Experimental details (ESI Methods) of the optic axis orientation of TiO<sub>2</sub> nanocylinders, Cr etch mask fabrication, surface functionalization and its evaluation using fluorescence microscopy, preparation of DNA constructs, assembly of flow cells, bioconjugation of TiO<sub>2</sub> nanocylinders, OTW instrumentation and measurements; TiO<sub>2</sub> dry etching optimization and the etching parameters employed (Tables S1 and S2); dimensional analysis of TiO<sub>2</sub> nanocylinders (Table S3); diverse applications of TiO<sub>2</sub> at the nanoscale (Fig. S1); selection of etch mask material (Fig. S2); control of sidewall profiles in TiO<sub>2</sub> etching (Fig. S3); size distributions of TiO<sub>2</sub> nanocylinders (Fig. S4); quantitative comparisons of different surface linker molecules (Fig. S5); DLS measurements on TiO<sub>2</sub> nanocylinders (Fig. S6); optical trap calibration (Fig. S7); and supplementary references. See DOI: 10.1039/c6nr00898d



Mainstream bottom-up approaches for TiO<sub>2</sub> nanofabrication,<sup>21</sup> *e.g.* the hydrothermal growth method<sup>1,22</sup> and electrochemical anodization,<sup>6</sup> although capable of high throughput, lack sufficient flexibility in controlling dimensions and geometries. A number of bottom-up methods are capable of fabricating single-crystal TiO<sub>2</sub> nanostructures, but these lack control of the crystallographic orientations and are limited to a certain crystalline polymorph, *e.g.* anatase<sup>23</sup> or rutile.<sup>15</sup> Hybrid fabrication methods, such as the atomic layer deposition array defined by etch-back technique,<sup>24,25</sup> can achieve a high aspect-ratio but are limited to the fabrication of amorphous or polycrystalline TiO<sub>2</sub>.<sup>26</sup> These limitations can be overcome by employing top-down nanofabrication methods based on plasma etching, which can target a single-crystal TiO<sub>2</sub> substrate with any desired crystalline polymorph or crystallographic orientation. However, as TiO<sub>2</sub> is substantially more difficult to etch than comparable materials (*e.g.*, silicon (Si), silicon dioxide (SiO<sub>2</sub>), and silicon nitride (Si<sub>3</sub>N<sub>4</sub>)),<sup>27,28</sup> such etching processes are currently limited to a low aspect-ratio and a largely positive sidewall angle.

Second, it is key to achieve highly efficient surface functionalization and bioconjugation of TiO<sub>2</sub> for applications such as (bio)sensors,<sup>29</sup> force transducers,<sup>30</sup> and torque transducers.<sup>31</sup> However, surface functionalization of TiO<sub>2</sub>, using common alkoxysilane surface linkers, is known to be less efficient in terms of linker density and uniformity than other oxide materials (*e.g.*, SiO<sub>2</sub> and aluminum oxide (Al<sub>2</sub>O<sub>3</sub>)).<sup>32,33</sup> Furthermore, the majority of the described bioconjugation methods for TiO<sub>2</sub> surfaces require a long incubation time and additional crosslinker molecules<sup>29</sup> that could decrease the overall conjugation efficiency and harm the biomolecule functionality. Peculiarly for single-crystal TiO<sub>2</sub> nanostructures, the lack of extensive quantitative and qualitative comparisons of different surface functionalization strategies hinders the selection of an optimal procedure.

Here, we present a successful top-down fabrication and surface functionalization of single-crystal TiO<sub>2</sub> nanostructures and nanoparticles. We focus our efforts on the rutile polymorph of single-crystal TiO<sub>2</sub> (100), in order to harness its exceptionally large optical birefringence and precisely oriented optic axis for effective torque transfer (ESI Methods†) in an optical torque wrench (OTW).<sup>20</sup> Using high aspect-ratio nanocylinders suitable for optical trapping as our target structures, we demonstrate how these can be mass-produced with well-defined sizes and etch profiles that display excellent overall structural uniformity. We achieve a dense, uniform surface coating of TiO<sub>2</sub> nanocylinders using different linker molecules, and we demonstrate subsequent covalent conjugation of biological and organic molecules such as DNA, streptavidin, biotin, and biocompatible poly(ethylene glycol) (PEG). We successfully exploit these developments to fabricate and functionalize TiO<sub>2</sub> nanocylinders with single DNA molecules, and demonstrate full rotational control of individual nanocylinders in an OTW. This provides a particularly stringent test, as proper functioning of the OTW relies on both the correctly oriented optic axis and tightly controlled dimension of the single-crystal TiO<sub>2</sub> nano-

cylinder, and the quality and reliability of the surface coating. Rutile being the polymorph of TiO<sub>2</sub> that is most difficult to etch,<sup>34</sup> our approach provides the means for increased exploitation of the superior material properties of single-crystal TiO<sub>2</sub> in any desired polymorph for diverse applications.

## Results and discussion

### Selecting an etch mask for the plasma etching of single-crystal TiO<sub>2</sub>

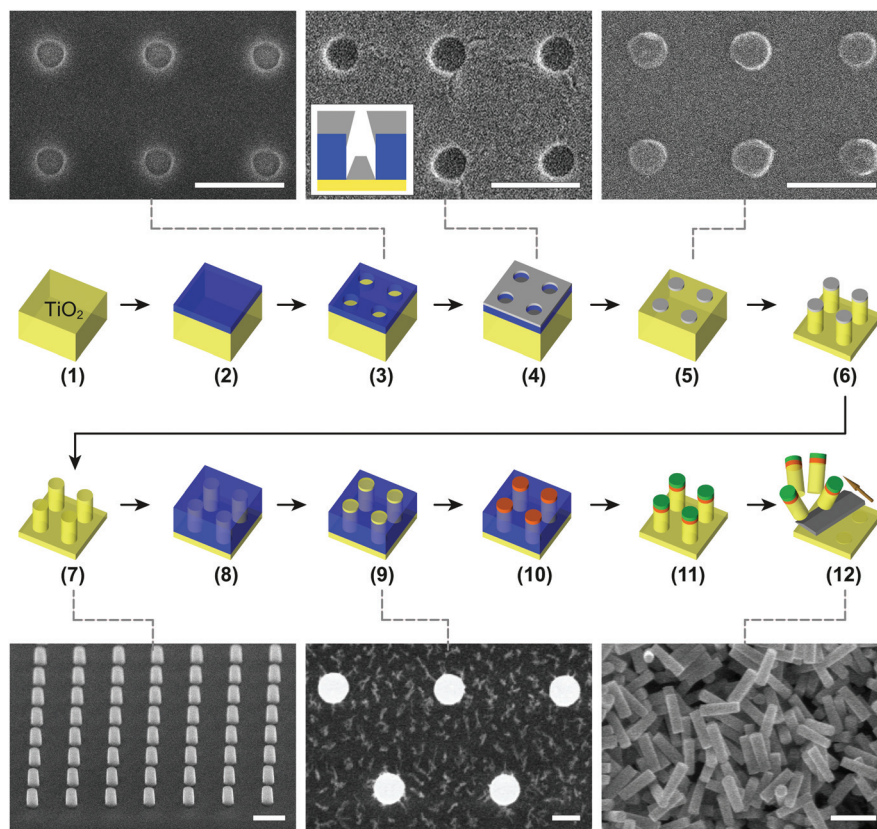
One of the major issues in top-down nanofabrication of single-crystal TiO<sub>2</sub> is its high etch resistance. Plasma generated by fluorine-based gases is capable of etching TiO<sub>2</sub> only under more aggressive etching conditions – in terms of plasma ion density and energy – than the ones employed for the dry etching of comparable materials *e.g.* Si, SiO<sub>2</sub>, and Si<sub>3</sub>N<sub>4</sub>. The increased difficulty in etching TiO<sub>2</sub> compared to *e.g.* SiO<sub>2</sub> stems from differences in the volatility of their etch byproducts: whereas SiF<sub>x</sub> is volatile, TiF<sub>x</sub> is not.<sup>27</sup> The more aggressive physical etching conditions for TiO<sub>2</sub> necessitate careful selection of the etch mask material: while a typical polymer-based mask (*e.g.*, photoresist, electron beam (e-beam) resist, or polystyrene spheres) can provide sufficient etch selectivity (defined as the ratio of the substrate and mask etch rates) for *e.g.* SiO<sub>2</sub>,<sup>31</sup> this is not the case for TiO<sub>2</sub>. The low etch selectivity imposes a thicker mask for a target etch depth, which is challenging as the applicable mask thickness is always limited (ESI Methods†). Also, masks can suffer from excessive edge erosion during etching, which in turn reduces both feature sizes and the ability to perform anisotropic etching.<sup>35</sup>

To overcome these challenges, we have searched for a mask material for the dry etching of single-crystal TiO<sub>2</sub> that achieves sufficiently high etch selectivity to permit the fabrication of nanostructures in a wide range of dimensions and sidewall profiles. We have compared different mask materials (Fig. S2†), such as chromium (Cr),<sup>36</sup> tungsten (W), e-beam resist, and amorphous Si. We observe that in particular Cr provides a significantly higher etch selectivity in fluorine-based etching of rutile TiO<sub>2</sub> (up to ~28 : 1 under specific etching conditions; an overview of etch selectivity values for different etching conditions can be found in Fig. S3†) than the other tested materials. We therefore select Cr as an appropriate etch mask material. To fabricate the Cr mask, we create circular apertures in a poly(methyl methacrylate) (PMMA) layer using e-beam lithography (Fig. 1, steps 1–3). The aperture diameters can be tuned within 100–600 nm by means of defocusing e-beam. Subsequent Cr deposition and the following lift-off define the mask (Fig. 1, steps 4 and 5).

### Trifluoromethane (CHF<sub>3</sub>)-based plasma etching of single-crystal TiO<sub>2</sub> nanocylinders

With the objective to maximize the etch rate with a sufficiently high etch selectivity (>10 : 1, in order to achieve etch depths up to 1–2 μm at the practical upper limit of Cr mask thickness, ~150 nm; ESI Methods†) and to produce single-crystal TiO<sub>2</sub>





**Fig. 1** Schematic diagram of the fabrication protocol for single-crystal TiO<sub>2</sub> nanostructures and nanoparticles. Each SEM image is linked to the corresponding step by a gray dashed line. Scale bars denote 500 nm. (Step 1) Cleaning of a single-crystal TiO<sub>2</sub> substrate (yellow). (Step 2) PMMA (blue) spin-coating for e-beam lithography. (Step 3) E-beam patterning and subsequent development to generate evaporation windows that define the desired nanostructure sizes. The corresponding SEM image in the inset shows the TiO<sub>2</sub> surfaces (circles) following exposure and development of the PMMA layer. (Step 4) Deposition of the Cr layer (light gray) through evaporation. The Cr layer covers both the accessible TiO<sub>2</sub> surfaces (circles) and the PMMA layer (inset SEM image). The inset illustration shows a cross-section that highlights the formation of a Cr mask. (Step 5) Lift-off of the PMMA layer and the resulting Cr etch mask. The SEM image in the inset displays the Cr mask (circles) formed on the TiO<sub>2</sub> substrate. (Step 6) Dry etching step to obtain the desired heights and sidewall profiles. (Step 7) Removal of the Cr mask following usage generates the complete nanostructures, and surface cleaning prepares these for subsequent surface functionalization. The SEM image (60° tilt) in the inset shows an array of the fabricated nanocylinders. (Step 8) Spin-coating of a temporary PMMA layer for area-selective functionalization. (Step 9) Etching of the temporary PMMA layer renders the tops of the nanostructures accessible. The SEM image in the inset shows the TiO<sub>2</sub> nanostructures (white circles) amidst the etched PMMA layer. (Step 10) Selective surface functionalization with linker molecules (orange). (Step 11) Removal of the temporary PMMA layer and the following conjugation with biomolecules (green). (Step 12) Mechanical cleavage of the nanostructures using a microtome blade (dark gray) to generate isolated individual nanoparticles. The inset shows an SEM image of a batch of cleaved nanocylinders. For further details, see Methods.

nanocylinders with vertical sidewall angles, we have optimized parameters for the fluorine-based plasma etching process (Fig. 1, step 6). We start with a reactive ion etching (RIE) system in which trifluoromethane (CHF<sub>3</sub>) is the major etchant, and oxygen (O<sub>2</sub>) and argon (Ar) are additive gases. The major etchant gas CHF<sub>3</sub> supplies both the reactive etching species and the fluorocarbon (C<sub>x</sub>F<sub>y</sub>) surface passivation layer-forming species.<sup>37</sup> To optimize the process, we systematically vary the radio frequency (RF) power, chamber pressure, and ratios of the etch gases (CHF<sub>3</sub>:O<sub>2</sub>:Ar) (Table S1†). Our optimized etching conditions (Table S2†) result in a high single-crystal TiO<sub>2</sub> etch rate of ~40 nm min<sup>-1</sup> at a sufficient etch selectivity of ~14:1 over the Cr mask, which enables the formation of TiO<sub>2</sub> nanocylinders with vertical sidewalls (~90°; Fig. 2a). We have successfully implemented this protocol on a second, nominally identical RIE system (Fig. 2b), requiring only minor

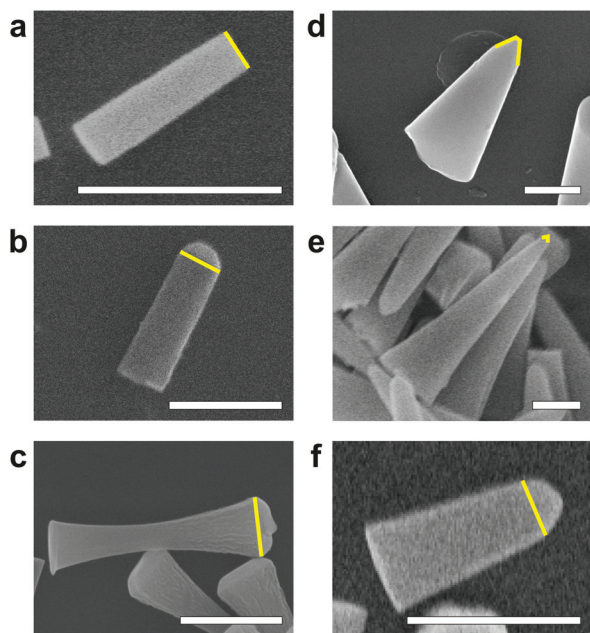
tuning in the O<sub>2</sub> flow rate (4–8 sccm compared to ~0.5 sccm), most likely due to differences in instrument calibration.

Notably, we observe that tuning a single process parameter, namely the O<sub>2</sub> flow rate, allows us to drastically alter sidewall etch profiles and even cross-sectional shapes (Fig. S3†). For example, at low O<sub>2</sub> flow rates (0–1 sccm), we can modulate the sidewall angles from positive to negative, thereby including vertical sidewalls (Fig. 2a and b). At significantly higher O<sub>2</sub> flow rates (5–10 sccm), we can obtain hourglass-shaped etch profiles (Fig. 2c).

#### Sulfur hexafluoride (SF<sub>6</sub>)-based plasma etching of single-crystal TiO<sub>2</sub> nanocylinders

While maintaining identical objectives as above (high etch selectivity and vertical sidewall angles), we have also optimized the plasma etching of TiO<sub>2</sub> using another major etchant,





**Fig. 2** Control of single-crystal  $\text{TiO}_2$  nanocylinder shapes using different conditions in plasma etching. In each SEM image, the top surface of the nanocylinder is marked by a yellow line (remnants of the Cr mask prior to its removal are visible in (b, c and f)). Scale bars denote 500 nm. In the following, the height ( $H$ ), the averaged diameter ( $D$ ), and the resulting aspect-ratio ( $\text{AR} = H/D$ ) of each nanocylinder are shown. (a) A nanocylinder with a vertical sidewall ( $89^\circ$ ) that results from an optimized  $\text{CHF}_3 : \text{O}_2$  dry etching in an RIE system ( $H$ : 430 nm,  $D$ : 110 nm,  $\text{AR}$ : 3.9). (b) A nanocylinder with a vertical sidewall ( $89^\circ$ ) etched from the optimized  $\text{CHF}_3 : \text{O}_2$  dry etching in a second, nominally identical RIE system ( $H$ : 605 nm,  $D$ : 205 nm,  $\text{AR}$ : 3.0). (c) An hourglass-shaped nanocylinder that results from  $\text{CHF}_3 : \text{O}_2 : \text{Ar}$  dry etching in an RIE system ( $H$ : 1020 nm,  $D$ : 200 nm,  $\text{AR}$ : 5.1). (d) A cone-shaped nanocylinder that results from  $\text{SF}_6 : \text{CH}_4 : \text{Ar}$  dry etching in an ICP-RIE system ( $H$ : 1385 nm,  $D$ : 490 nm,  $\text{AR}$ : 2.8). (e) A cone-shaped nanocylinder that results from  $\text{SF}_6 : \text{He}$  dry etching in an ICP-RIE system ( $H$ : 2160 nm,  $D$ : 390 nm,  $\text{AR}$ : 5.5). (f) A nearly vertical ( $85^\circ$ ) nanocylinder that results from an optimized  $\text{SF}_6 : \text{He}$  dry etching in an ICP-RIE system ( $H$ : 470 nm,  $D$ : 210 nm,  $\text{AR}$ : 2.2).

sulfur hexafluoride ( $\text{SF}_6$ ), in inductively coupled plasma (ICP)-RIE systems. We achieve higher etch rates of  $100\text{--}200 \text{ nm min}^{-1}$  (compared to those of  $30\text{--}100 \text{ nm min}^{-1}$  in RIE systems) using two different ICP-RIE systems (one equipped with  $\text{SF}_6$ , methane ( $\text{CH}_4$ ), and Ar gases, Fig. 2d; the other equipped with  $\text{SF}_6$  and helium (He) gases, Fig. 2e and f), making it possible to fabricate  $\text{TiO}_2$  nanocylinders with heights up to  $1\text{--}2 \mu\text{m}$  while reducing the time of exposure to the plasma. The latter is important because longer etch durations tend to induce a drift in the etching conditions which in turn leads to irregular etch profiles. The higher  $\text{TiO}_2$  etch rates that we obtain result from the increased density of plasma generated in ICP-RIE *versus* RIE systems<sup>28</sup> and a reduced level of  $\text{C}_x\text{F}_y$  sidewall surface passivation. Decreased levels of  $\text{C}_x\text{F}_y$  passivation are attributed to an excess of hydrogen plasma<sup>38</sup> and to the lack of a carbon source for the cases of  $\text{SF}_6 : \text{CH}_4 : \text{Ar}$  and  $\text{SF}_6 : \text{He}$ , respectively. Furthermore,  $\text{SF}_6$ -etched nanocylinders show cleaner, smoother

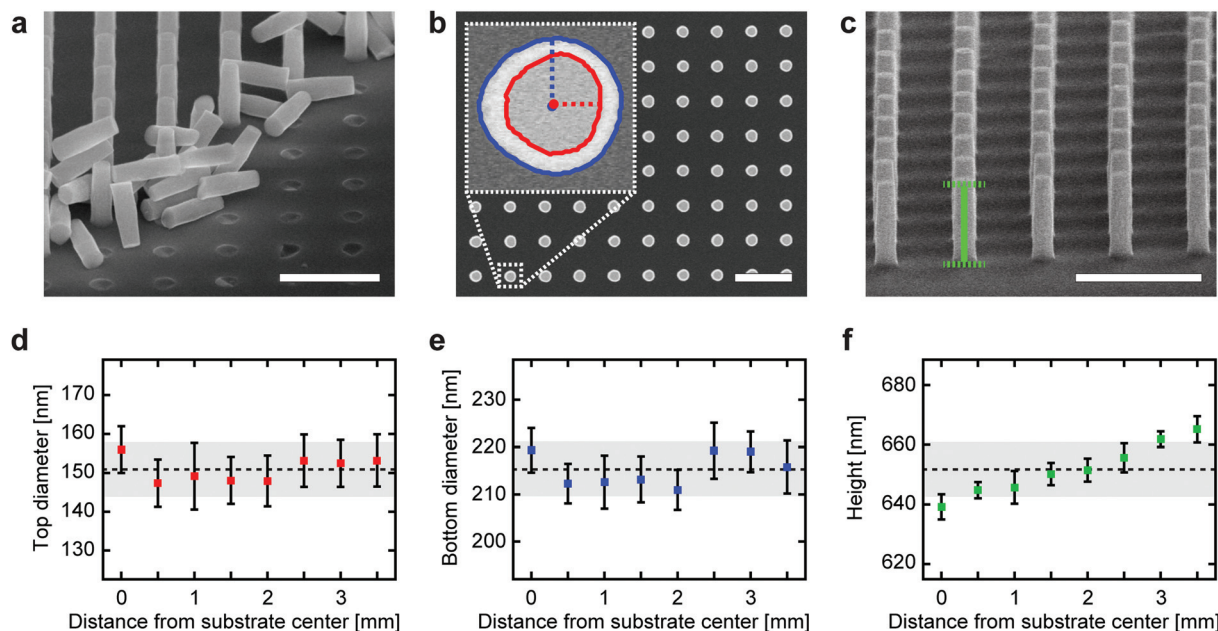
surfaces in high-resolution scanning electron microscopy (SEM) images (Fig. 2d) compared to those of  $\text{CHF}_3$ -etched cylinders (Fig. 2c).

When we use non-optimized  $\text{SF}_6$ -based plasma etching conditions, etch profiles displaying highly positive sidewall angles are obtained. Since the high plasma densities of ICP-RIE systems also significantly increase the Cr etch rates, we observe that the Cr mask tends to be completely etched away during the process, hence resulting in the formation of cone-shaped nanocylinders<sup>35</sup> (Fig. 2d and e). Under our optimized etching conditions (Table S2†), which rely on a reduced ICP power to generate moderate plasma density, we are able to achieve sufficient etch selectivity over the Cr mask ( $\sim 16:1$ ) and nearly vertical sidewall angles ( $\sim 85^\circ$ ; Fig. 2f) with high single-crystal  $\text{TiO}_2$  etch rates of  $\sim 120 \text{ nm min}^{-1}$ .

### Quantification of single-crystal $\text{TiO}_2$ nanocylinder uniformity

To quantify both the local and global structural uniformity of fabricated single-crystal  $\text{TiO}_2$  nanocylinders over an entire substrate, we have analyzed SEM images of high aspect-ratio (3.6) nanocylinders fabricated using the  $\text{CHF}_3$  plasma-based protocol (Fig. 3; etching conditions in Table S2†). Qualitatively, the high uniformity of nanocylinder diameters and heights can be observed from the SEM image of a cleaved nanocylinder substrate (Fig. 3a). To quantify this, we measure the dimensions of nanocylinders at radial distances from the substrate center out to 3.5 mm and spaced by 0.5 mm (thus covering the entire circularly patterned area with a radius of  $\sim 4 \text{ mm}$  on the  $10 \times 10 \text{ mm}^2$ -sized substrate). From the analysis of top-view SEM images (Fig. 3b), we observe that the top (Fig. 3d) and bottom diameters (Fig. 3e) exhibit excellent local uniformity, defined as the uniformity at each measurement position (averaged relative standard deviation (RSD) of 4.4% (top) and 2.3% (bottom)). The global uniformity across the substrate displayed similar values (RSD of 4.7% (top) and 2.7% (bottom)). Fluctuations in diameters likely result from the instability of the e-beam during the patterning process of the Cr etch mask. The observation that the top diameters are nonetheless slightly less uniform than the bottom diameters may result from the fact that etching erodes the Cr mask in a non-uniform fashion depending on the roughness of the mask surface,<sup>39</sup> as is backed up by an analysis of the roundness of the top and bottom nanocylinder surfaces (Fig. S4†). From tilted-view SEM images (Fig. 3c), we also extract the nanocylinder heights (Fig. 3f), which similarly show very good uniformity both locally (averaged RSD of 0.6%) and globally (RSD of 1.4%). We attribute the nearly monotonic increase in heights outward from the substrate center to the well-known loading effect, in which the transport and depletion of etching species along a substrate contribute to etch rate nonuniformity.<sup>40</sup> The analysis of a batch of low aspect-ratio (1.6) nanocylinders reveals identical trends (Fig. S4 and Table S3;† etching conditions in Table S2†), thereby proving that our protocol can be used to generate both low and high aspect-ratio nanoscale structures with high uniformity.





**Fig. 3** Dimensions of fabricated single-crystal TiO<sub>2</sub> nanocylinders. (a–c) SEM images of etched TiO<sub>2</sub> nanocylinders (light gray). Scale bars denote 1 μm. (a) Tilted-view (60°) of partially cleaved TiO<sub>2</sub> nanocylinders. An array of rigidly fixed nanocylinders is visible in the top-left corner, and the cleaved substrate surface is in the bottom-right corner. The released nanocylinders are positioned at the interface of these regions. (b) Top-view of the nanocylinders. The inset shows the boundaries of the top (red contour line) and bottom (blue contour line) surface areas detected using the custom-written image analysis software routine. The dotted horizontal red (vertical blue) line and the red (blue) dot display the equivalent radius and the center of the top (bottom) surface, respectively. (c) Tilted-view (75°) together with an illustration of the image analysis procedure used to extract nanocylinder heights. The green vertical line measures the distance between the centers of the top and bottom surfaces (indicated by the green dotted horizontal lines). This distance is converted to the actual height using the tilting angle. (d–f) Quantification of nanocylinder diameters and heights over the substrate. Measurement points are spaced by 0.5 mm from the center of the substrate to its edge. At each point, the diameters (heights) are calculated from  $n = 12$  ( $n = 10$ ) different nanocylinders. The square markers and the error bars in the graphs represent the mean and the standard deviation of the local uniformity, respectively. The horizontal dotted black lines and the top and bottom sides of the gray shaded boxes in the graphs represent the mean and the standard deviation of the global uniformity, respectively. (d) Top diameters, (e) bottom diameters, and (f) heights are shown as a function of distance from the substrate center.

### Surface functionalization and bioconjugation of single-crystal TiO<sub>2</sub>

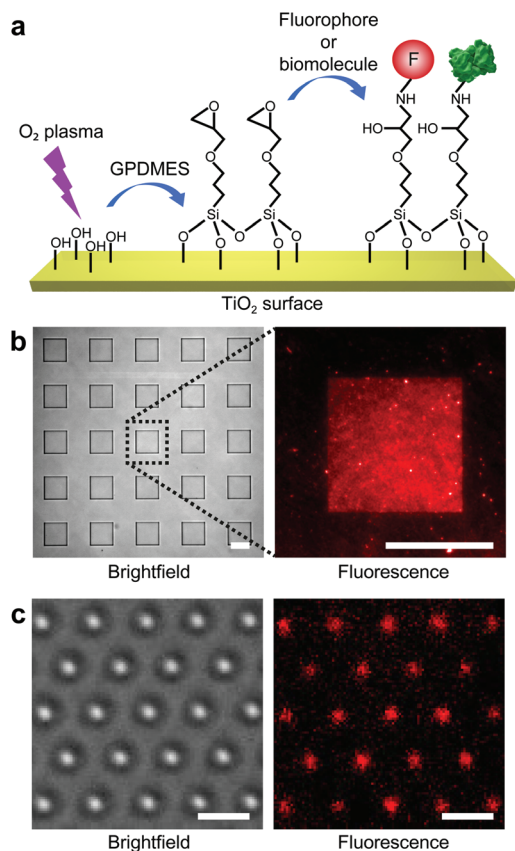
We now demonstrate highly efficient and versatile surface functionalization and bioconjugation of single-crystal rutile TiO<sub>2</sub> (Fig. 4a). We perform the functionalization experiments on single-crystal TiO<sub>2</sub> nanostructures fabricated using our developed SF<sub>6</sub>-based plasma etching process presented earlier. Compared with CHF<sub>3</sub>-based etching, this process results in a lower degree of surface contamination by C<sub>x</sub>F<sub>y</sub>, and hence a higher surface linker coverage.

To quantitatively characterize the surface coating efficiency of different covalently bound surface linkers, we first test functionalization on single-crystal rutile TiO<sub>2</sub> substrates with large-scale square micro-patterns (25 × 25 μm<sup>2</sup>) embedded in a thick (1–2 μm) PMMA layer (Fig. 4b). Similarly to other oxide materials, the surface of TiO<sub>2</sub> is populated by hydroxyl groups that allow it to be functionalized with different types of linker molecules, such as silanes and other organic molecules with a covalent hydroxyl-binding capacity.<sup>33,41</sup> Here, we have tested four different surface linker molecules: an aminoalcohol (ethanolamine hydrochloride; ETA), an epoxysilane ((3-glycid-

oxypropyl)dimethylethoxysilane; GPDMS), a widely used alkoxy silane ((3-aminopropyl)dimethylethoxysilane; APDMES), and a cyclic azasilane (*N*-*n*-butyl-aza-2,2-dimethoxysilacyclopentane; BADMSCP). Additionally, since PEG coatings are widely used for surface passivation<sup>42</sup> and as biocompatibility layers,<sup>43</sup> we have also tested the covalent attachment of hetero-bifunctional PEG to ETA-coated surfaces (ESI Methods, Fig. S5†). To compare the coating efficiency of these different linkers, we covalently bind fluorophores (ATTO 647N;  $\lambda_{\text{excitation}} = 640$  nm,  $\lambda_{\text{emission}} = 669$  nm) to the functionalized micro-patterns and measure the fluorescence intensity using quantitative fluorescence microscopy (ESI Methods†). The fluorescence measurements report successful surface functionalization for all the surface linkers used (Fig. S5†).

Regarding subsequent bioconjugation to TiO<sub>2</sub> surfaces, several considerations led us to select epoxysilane (GPDMS) as the most appropriate surface linker. To start, epoxysilanes are widely used for their demonstrated reliability in surface functionalization<sup>44</sup> and biomolecule attachment.<sup>45</sup> Furthermore, GPDMS-coated TiO<sub>2</sub> surfaces demonstrate high surface linker coating density and homogeneity (Fig. 4b). Indeed, while GPDMS coatings provide a slightly lower surface linker





**Fig. 4** Characterization of the efficiency of surface functionalization of single-crystal TiO<sub>2</sub> structures using fluorescence microscopy. (a) Illustration of the surface coating steps. First, single-crystal TiO<sub>2</sub> surfaces are O<sub>2</sub> plasma-treated to generate hydroxyl groups (–OH). Then epoxy-silanes (GPDMES) are covalently bound to the surface hydroxyl groups. Consequently, either fluorophores (red) or biomolecules (e.g., streptavidin (green)) are bound covalently to the reactive epoxy functional group. (b) Functionalized micro-patterns for the quantitative characterization of the efficiency of surface functionalization. The brightfield image (left panel) shows squares (25 × 25 μm<sup>2</sup>) patterned on the PMMA-coated TiO<sub>2</sub> substrate. The corresponding zoom-in fluorescence image (right panel) of a square shows successful covalent binding of the amino-labeled fluorophores (ATTO 647N) to the epoxysilane functionalized surface. Scale bars denote 20 μm. (c) Functionalized nanostructures for the qualitative characterization of the efficiency of surface functionalization. Brightfield (left panel) and the corresponding fluorescence (right panel) images of top-area functionalized TiO<sub>2</sub> nanocylinders using the same method as above. Scale bars denote 2 μm.

density than ETA or PEGylated ETA coatings, their coating efficiency is significantly higher than the one obtained using BADMSCP and comparable to that of commonly used APDMES (Fig. S5†).

More importantly, the greatest advantages of using GPDMES compared to other surface linkers are: first, the ability of the epoxy group to react directly with the primary amino groups of biomolecules that permits bioconjugation in the absence of additional crosslinkers, avoiding conditions that could harm the structural and functional integrity of the target biomolecules; and second, the rapid surface functional-

ization process (e.g., ~15 min compared to ~12 h of all the other linkers; ESI Methods†). With this procedure in hand, epoxysilane-functionalized TiO<sub>2</sub> surfaces can be readily used for the covalent conjugation of a majority of biomolecules. We apply this bioconjugation process to the single-crystal TiO<sub>2</sub> nanocylinder arrays on the substrate (Fig. 1, steps 7–11) prior to their mechanical cleaving (Fig. 1, step 12) to avoid additional, subsequent purification procedures. At this stage, functionalization can be applied to specific areas of the TiO<sub>2</sub> nanocylinders through partial PMMA coating (Fig. 1, steps 8–10). Using this approach, we are able to functionalize and bioconjugate only the top parts of the TiO<sub>2</sub> nanocylinders (Fig. 1, step 11). Fluorescence microscopy has also been used to qualitatively demonstrate the successful functionalization of individual TiO<sub>2</sub> nanocylinders (Fig. 4c).

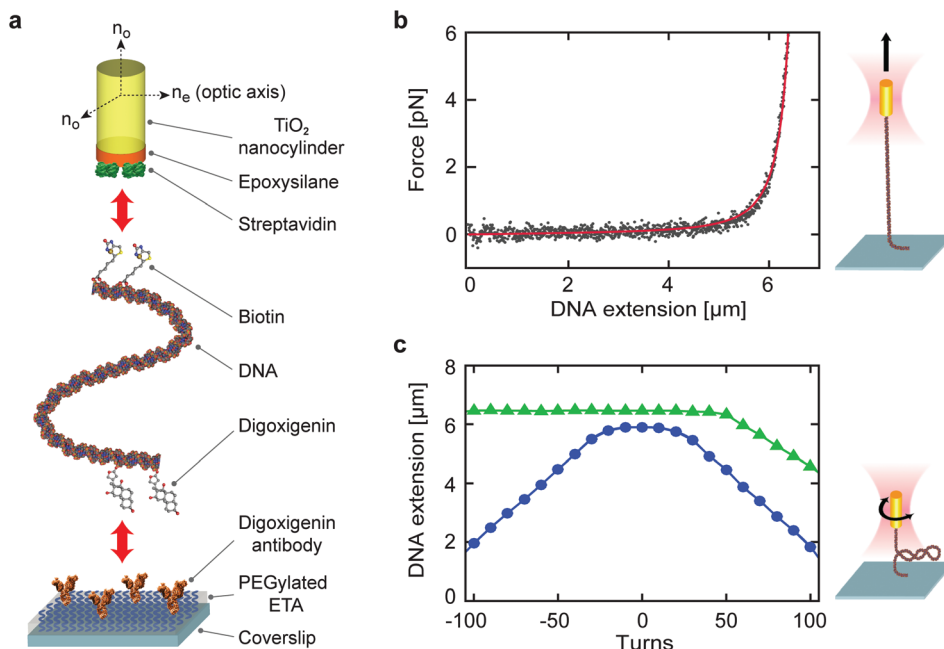
### Degree of monodispersity in coated single-crystal TiO<sub>2</sub> nanoparticles

Our ability to functionalize single-crystal TiO<sub>2</sub> nanoparticles with high surface linker density and homogeneity can also be beneficial in different contexts. For example, following the mechanical cleaving that liberates the nanocylinders from the TiO<sub>2</sub> substrate, it is necessary to prevent their aggregation in aqueous environments. Generally speaking, the aggregation of nanoparticles depends on both the surface composition of the nanoparticles and the type of solution in which they are immersed.<sup>46</sup> We have tested different surface coatings and buffer solutions that effectively prohibit single-crystal TiO<sub>2</sub> nanoparticle aggregation and have evaluated these using dynamic light scattering (DLS) measurements (Fig. S6†). We found that non-coated TiO<sub>2</sub> nanocylinders aggregate substantially over time in deionized (DI) water, in contrast to what occurs in physiological phosphate buffered saline (PBS) solution at a similar pH (7.4). We also found that the addition of bovine serum albumin (BSA, 2% (m/v)), which is widely used as a surface passivation agent,<sup>47</sup> deteriorates substantially the monodispersity of TiO<sub>2</sub> nanocylinders in both DI water and PBS solution. When we apply a PEG coating – widely implemented for passivating nanoparticle surfaces to decrease aggregation and for enhancing their biocompatibility<sup>43</sup> – to TiO<sub>2</sub> nanocylinders, we observe no aggregation in either DI water or PBS solution. Such PEG-coated TiO<sub>2</sub> nanocylinders refrain from aggregation even when they are conjugated to biomolecules such as biotin or DNA. Likewise, the GPDMES-coated TiO<sub>2</sub> nanocylinders with bioconjugated streptavidin show no aggregation under physiological conditions (PBS solution) and therefore have been chosen for the single-molecule OTW experiments.

### Characterization of individual DNA molecules using single-crystal TiO<sub>2</sub> nanocylinders

To demonstrate the potential of our developed fabrication and surface coating processes for diverse applications, we tether single-crystal TiO<sub>2</sub> nanocylinders to individual linear, double-stranded DNA molecules and perform stretching and twisting experiments in an OTW. For these measurements, we use





**Fig. 5** Application of DNA-tethered single-crystal rutile  $\text{TiO}_2$  nanocylinders in an OTW. (a) Schematic of a DNA tethered at one extremity to a single-crystal rutile  $\text{TiO}_2$  nanocylinder and at the other extremity to a flow cell channel surface. For the nanocylinder, the orientations of ordinary ( $n_o$ ) and extraordinary ( $n_e$ ) refractive indices are indicated. First, we functionalize the flow cell channel surface with ETA, PEG, and digoxigenin antibodies. Then the end of the DNA containing the digoxigenin-enriched handle is attached to the flow cell channel surface via antigen-antibody binding. The other extremity of the DNA that contains the biotin-enriched handle binds to the streptavidin-coated nanocylinder. (b) The extension of tethered DNA as a function of force. The gray dots represent force-extension data while the red line is a fit to the WLC model. The illustration depicts a fully stretched DNA. (c) The response of DNA to rotation at different stretching forces (blue circles and green triangles for 0.5 pN and 1.8 pN, respectively). The corresponding illustration represents a supercoiled DNA.

GPDME-functionalized, streptavidin-coated single-crystal  $\text{TiO}_2$  nanocylinders fabricated in  $\text{SF}_6$  plasma (Methods), and test their response to force and torque applied on torsionally constrained 20.6 kbp DNA (contour length of  $\sim 7 \mu\text{m}$ ; ESI Methods†). A biotinylated handle on one extremity of the DNA is designed to bind to the streptavidin-coated nanocylinders, whereas the other extremity of the DNA includes digoxigenin to allow it to bind to the digoxigenin antibodies that are covalently bound to a heterobifunctional PEG-coated flow cell channel (Fig. 5a, ESI Methods†).

Prior to performing measurements on these DNA-tethered single-crystal  $\text{TiO}_2$  nanocylinders in an OTW (ESI Methods†), we calibrate the optical trap by using individual non-tethered nanocylinders to measure its trap stiffness (Fig. S7†). We can then apply a force to a tethered nanocylinder and stretch the DNA (Fig. 5b). The obtained force-extension data are fitted to the worm-like chain (WLC) model<sup>48</sup> (red line in Fig. 5b) and yield a persistence length of  $45 \pm 1 \text{ nm}$  and a contour length of  $6.8 \pm 0.2 \mu\text{m}$  (means and standard deviations for  $n = 5$  different DNA tethers), in excellent agreement with previous reports.<sup>30,31,48</sup> We additionally rotate the nanocylinder at low constant force (0.5 pN) or medium constant force (1.8 pN) to supercoil the tethered DNA molecule. The resulting extension-rotation relationship (Fig. 5c) shows the characteristic symmetric (asymmetric) response of twisted DNA in the low (medium) force regime, also in agreement with previous

reports.<sup>31,49–52</sup> We note that the OTW provides an excellent platform to evaluate the quality of our top-down fabrication of single-crystal  $\text{TiO}_2$  nanostructures, as only nanocylinders with precisely controlled dimensions and uniformity are appropriate for stable and reproducible optical trapping. Furthermore, the use of the OTW to stretch and twist DNA molecules provides a stringent test of the applied surface functionalization, as these processes (notably twisting) are only possible provided that the surface functionalization and bioconjugation processes are sufficiently efficient to allow for the formation of multiple stable bonds at either DNA extremity.<sup>52</sup>

## Conclusions

We have developed and optimized processes for the fabrication, surface functionalization, and bioconjugation of single-crystal  $\text{TiO}_2$  nanostructures and nanoparticles. Using two top-down etching approaches, we demonstrate the fabrication of highly uniform nanostructures and nanoparticles with controllable shapes and dimensions. The  $\text{CHF}_3$ -based etching process provides a wider range of etch geometries, while the  $\text{SF}_6$ -based etching process results in improved surface quality allowing homogeneous and dense coating. We are able to etch single-crystal  $\text{TiO}_2$  into various nanoscale shapes, including cylinders, cones, and hourglass-shaped structures. The fabricated



nanostructures have diameters in the range of 100–600 nm, with heights up to 1–2  $\mu\text{m}$  under etching conditions that yield high etch rate and selectivity. Using  $\text{SF}_6$ -etched single-crystal  $\text{TiO}_2$  nanocylinders, we show how they can be functionalized with high efficiency and be conjugated covalently to a majority of biomolecules. We demonstrate the use of these coated  $\text{TiO}_2$  nanocylinders by stretching and twisting individually tethered DNA molecules, an application that exploits the tight dimensional control and high quality surface functionalization of nanocylinders etched from a rutile (100) single-crystal  $\text{TiO}_2$  substrate. Our developed fabrication and surface functionalization methods will likely find utilization in diverse optical and electronic applications of single-crystal  $\text{TiO}_2$ , including applications in life science-oriented fields through *e.g.* the development of biosensors and single-molecule techniques.

## Methods

### Fabrication and bioconjugation of single-crystal rutile $\text{TiO}_2$ nanocylinders for OTW experiments

We use single-side polished single-crystal rutile  $\text{TiO}_2$  (100) substrates (Latech, Singapore),  $10 \times 10 \text{ mm}^2$  in size and 0.5 mm in thickness, to produce nanocylinders. We clean the substrates in fuming nitric acid (99.5%, Sigma-Aldrich, The Netherlands) using ultrasonication for 10 min followed by thorough rinsing in DI water and drying under a nitrogen ( $\text{N}_2$ ) stream (Fig. 1, step 1). We then subject the substrates to an  $\text{O}_2$  plasma (TePla300, PVA TePla, Germany), after which we spin-coat a  $\sim 250 \text{ nm}$ -thick e-beam resist layer (PMMA 950k A4, MicroChem, Germany) at 500 rpm for 5 s and then 3000 rpm for 55 s. We bake the resist-coated substrates on a hotplate for 30 min at  $175 \text{ }^\circ\text{C}$  (Fig. 1, step 2). The substrates do not require an additional conductive layer to prevent charge accumulation during e-beam patterning since it has sufficiently high electrical conductivity.

We then use an e-beam patterning system (EBPG 5000+, Leica, UK; the acceleration voltage is set to 100 kV and the aperture diameter to 400  $\mu\text{m}$ ) to pattern the PMMA layer by a defocused e-beam with circular cross-section and tunable diameter. The patterning of each circular shape is performed by a single-pixel e-beam exposure, defining the shapes of the Cr mask for subsequent nanocylinder etching. Using optimized e-beam conditions (a current of 85 nA, a defocusing of 100–200 nm, and a dose of  $2000 \mu\text{C cm}^{-2}$ ), we pattern circles with 600 nm pitch on a circular patterning area with radius  $\sim 4 \text{ mm}$  ( $\sim 140$  million masks in total) in  $<30 \text{ min}$ . We develop the patterned substrate using a solution of methyl isobutyl ketone (MIBK, Sigma-Aldrich, The Netherlands) and isopropyl alcohol (IPA, Sigma-Aldrich, The Netherlands) (1 : 3 MIBK : IPA) for 60 s with constant hand agitation at room temperature. We then rinse the substrate in IPA for 30 s and dry it under a  $\text{N}_2$  stream (Fig. 1, step 3).

We deposit the Cr mask layer using either an e-beam evaporator (Temescal FC-2000, Ferrotec, Germany) or a thermal evaporator (L560, Leybold Heraeus, Germany) loaded with Cr pieces (purity of 99.95%, Kurt J. Lesker, Germany), using the

patterned PMMA layer as evaporation windows. We use slow Cr deposition rates ( $\leq 1.0 \text{ \AA s}^{-1}$ ) to obtain high quality Cr layers (Fig. 1, step 4). We finalize Cr mask formation in a lift-off process by soaking the substrate into a preheated ( $80 \text{ }^\circ\text{C}$ ) resist stripper (PRS-3000, JTBaker, The Netherlands) for 20 min with constant agitation using a magnetic spinner. Then we thoroughly rinse the substrate in DI water and dry it under a  $\text{N}_2$  stream (Fig. 1, step 5).

We etch  $\text{TiO}_2$  nanocylinders using the optimized conditions (Table S2†) for vertical sidewall angles (Fig. 1, step 6). We etch nanocylinders with either an RIE system (Fluor Z401S, Leybold Heraeus, Germany; Fig. 2a and b) or an ICP-RIE system (Plasmalab system 100, Oxford Instr., UK; Fig. 2f). For dimensional analysis of the etched nanocylinders, we employ SEM systems (Hitachi S4800 FESEM, FEI XL30S FEG SEM, or FEI Nova NanoSEM). We remove the used Cr mask using a wet etchant (Chromium Etchant N° 1, MicroChemicals, Germany) and then perform surface cleaning using fuming nitric acid and  $\text{O}_2$  plasma (TePla300) for the subsequent surface functionalization (Fig. 1, step 7).

Optionally, if area-selective functionalization on top of the nanocylinders is required, we cover their sidewalls with a temporary protection layer. We cover the substrate with a PMMA 950k resist at a chosen concentration to provide a spin-coated thickness larger than the heights of the nanocylinders (Fig. 1, step 8). Consequently, we etch the PMMA layer to render the tops of the nanocylinders accessible, using either  $\text{O}_2$  plasma (TePla300) or a MIBK solution (Fig. 1, step 9). Note that we do not bake the resist in order to allow for its straightforward removal afterwards.

To attach biomolecules to  $\text{TiO}_2$  nanocylinders, we first activate the nanocylinder substrates by  $\text{O}_2$  plasma treatment (Plasma-PREEN I, Plasmatic Systems Inc., USA). Then we bind GPDMS to the substrate for 15 min at  $75 \text{ }^\circ\text{C}$  using non-diluted GPDMS solution, and wash the substrate in chloroform (CHROMASOLV plus, for HPLC,  $\geq 99.9\%$ , Sigma-Aldrich, The Netherlands) three times for 15 s each, followed by drying under a  $\text{N}_2$  stream (Fig. 1, step 10). (If a temporary PMMA layer is used for area-selective functionalization, we first wash the substrate in ethanol three times for 15 s each directly after the incubation with GPDMS, followed by drying under a  $\text{N}_2$  stream. We then remove the temporary PMMA layer in chloroform for 15 min at room temperature, followed by an additional washing in fresh chloroform three times for 15 s each and drying under a  $\text{N}_2$  stream.)

We then bind streptavidin molecules to the epoxy group of GPDMS by incubating the nanocylinders with  $2 \mu\text{M}$  streptavidin (Sigma-Aldrich, The Netherlands) in PBS solution (pH 7.4, Sigma-Aldrich, The Netherlands) for 1 h at room temperature. After washing the substrate three times for 15 s each with PBS/TWEEN® solution (pH 7.4, PBS containing 0.1% (v/v) TWEEN® 20 (Sigma-Aldrich, The Netherlands)), we wash the substrate with PBS solution (pH 7.4) another three times for 15 s each (Fig. 1, step 11).

We cleave  $\text{TiO}_2$  nanocylinders mechanically from the substrate using a diamond microtome blade (DT315D50, C.L.





Sturkey, USA) inside a PBS/Triton™ droplet (pH 7.4, PBS containing 0.05% (v/v) Triton™ X-100 (Sigma-Aldrich, The Netherlands)), followed by suction of the droplet using a micropipette (Fig. 1, step 12). These cleaved, streptavidin-coated TiO<sub>2</sub> nanocylinders can be further coupled with biomolecules of interest, e.g. DNA with biotinylated handles, by incubating them in a flow cell channel for OTW experiments (ESI Methods†).

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## Supplementary Information

### Tunable Top-Down Fabrication and Functional Surface Coating of Single-Crystal Titanium Dioxide Nanostructures and Nanoparticles

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This document includes:

#### Supplementary Methods

Orientation of the optic axis in single-crystal rutile TiO<sub>2</sub> nanocylinder for OTW experiment.  
Considerations for optimal fabrication of the Cr etch mask for single-crystal TiO<sub>2</sub> etching.  
Surface functionalization procedure of single-crystal TiO<sub>2</sub>.  
Evaluation of single-crystal TiO<sub>2</sub> surface functionalization efficiency via fluorescence microscopy.  
Preparation of DNA construct for OTW experiments.  
Preparation of flow cell for OTW experiments.  
Bioconjugation of DNA to single-crystal TiO<sub>2</sub> nanocylinders for OTW experiments.  
OTW instrumentation and DNA measurements with single-crystal TiO<sub>2</sub> nanocylinders.

#### Supplementary Tables

**Table S1.** Dry etching conditions for single-crystal TiO<sub>2</sub> during optimization of the CHF<sub>3</sub>-RIE process.  
**Table S2.** Dry etching conditions for single-crystal TiO<sub>2</sub> nanofabrication.  
**Table S3.** Dimensional analysis of high and low aspect-ratio TiO<sub>2</sub> nanocylinders.

#### Supplementary Figures

**Fig. S1.** Diverse applications of TiO<sub>2</sub> at the nanoscale.  
**Fig. S2.** The etch rates and etch selectivities of different mask materials.  
**Fig. S3.** Control of sidewall profiles and etch characteristics in single-crystal TiO<sub>2</sub> nanocylinders by variation of O<sub>2</sub> flow rate in the CHF<sub>3</sub>-RIE process.  
**Fig. S4.** Dimensions of fabricated single-crystal TiO<sub>2</sub> nanocylinders.  
**Fig. S5.** Quantitative comparison of surface functionalization efficiencies on single-crystal TiO<sub>2</sub> for different linker molecules.  
**Fig. S6.** DLS measurements of single-crystal TiO<sub>2</sub> nanocylinder aggregation in relation to surface coatings and buffer conditions.  
**Fig. S7.** Optical trap calibration of single-crystal TiO<sub>2</sub> nanocylinders.

#### Supplementary References

## Supplementary Methods

### Orientation of the optic axis in single-crystal rutile TiO<sub>2</sub> nanocylinder for OTW experiment

To control polarization-based rotation of optically trapped nanoparticles in an OTW, birefringent positive uniaxial single-crystals are desirable substrate materials. Single-crystal rutile TiO<sub>2</sub> is such a material, and it has an exceptionally high birefringence that is advantageous for effective torque transfer in an OTW. In particular, cylindrically shaped nanoparticles align their long axis with the direction of laser beam propagation, fixing two of the three rotational degrees of freedom (DOF). The remaining rotational DOF is controllable via the polarization of the laser beam provided that the optic axis is perpendicular to the nanocylinder's long axis (**Fig. 5a**). To appropriately control the orientation of this optic axis within the nanocylinders, it is necessary to etch into (100)-cut single-crystal rutile TiO<sub>2</sub> substrates. A similar approach has been employed for the case of X-cut single-crystal quartz SiO<sub>2</sub> substrates.<sup>1-5</sup>

### Considerations for optimal fabrication of the Cr etch mask for single-crystal TiO<sub>2</sub> etching

We consider the optimal fabrication of the Cr etch mask for the desired size of single-crystal TiO<sub>2</sub> nanostructures. The deposited Cr layer should be sufficiently thick for the mask to remain functional until the end of etching process, taking into account the fact that the mask top surface will not be perfectly flat. Also, the overall thickness of the Cr mask is limited by that of the used PMMA layer. The thickness of the PMMA should be 2–3 times larger than that of the Cr mask to facilitate complete lift-off, but it has an upper limit determined by its concentration. In practice, Cr layers thicker than ~150 nm tend to cause more severe deformation in patterned PMMA layers, resulting in higher nonuniformity. This deformation is presumably due to the built-up stress in Cr layers during physical vapor deposition.<sup>6</sup> A further consideration in mask fabrication is that mask shapes tend to be more cone-like when thicker Cr layers and/or smaller patterned apertures are used<sup>7</sup> (**Fig. 1, step 4, inset illustration**). Such masks are not suitable for anisotropic etching for vertical sidewall due to more rapid erosion of their thinner edges.

### Surface functionalization procedure of single-crystal TiO<sub>2</sub>

For the surface functionalization of single-crystal TiO<sub>2</sub> substrates, we have compared four different surface linker molecules (**Fig. S5†**): ETA (Sigma-Aldrich, The Netherlands), GPDMS (Sigma-Aldrich, The Netherlands), APDMES (Sigma-Aldrich, The Netherlands), and BADMSCP (abcr GmbH, Germany). For the binding of ETA linker, we dissolve ETA in anhydrous dimethyl sulfoxide (DMSO) (Sigma-Aldrich, The Netherlands) to a final concentration of 5 M. We use this ETA/DMSO solution to incubate the substrates for 12 h at room temperature, followed by washing the substrates with DI water. For the binding of epoxysilane linker (GPDMS), we incubate the substrates for 15 min at 75 °C using non-diluted GPDMS solution, followed by chloroform washing. For the binding of the APDMES and BADMSCP linkers, we incubate the substrates in ethanol containing either 5% (v/v) of APDMES or BADMSCP. We carry out the silanization reaction for 12 h at 70 °C and then wash with chloroform (or ethanol). Additionally, we perform PEGylation of ETA-coated surfaces with heterobifunctional NHS-PEG-COOH (MW 5,000, LaysanBio, USA).<sup>8</sup> We incubate the surfaces with 2 mM PEG dissolved in 100 mM 2-(N-morpholino)ethanesulfonic acid (MES) buffer (pH 4.7, Sigma-Aldrich, The Netherlands) for 1 h at room

temperature. Afterwards, we wash the PEGylated surfaces with DI water. For every washing step involved, we wash three times for 15 s each, and then dry the substrates under a N<sub>2</sub> stream. The above protocols can also be applied to other oxidized surfaces, e.g. quartz (SiO<sub>2</sub>) (**Fig. S5†**), silicon (Si), silicon nitride (Si<sub>3</sub>N<sub>4</sub>), and non-noble metals.

#### **Evaluation of single-crystal TiO<sub>2</sub> surface functionalization efficiency via fluorescence microscopy**

We fabricate 25 × 25 μm<sup>2</sup> micro-patterns of PMMA on single-crystal rutile TiO<sub>2</sub> and quartz SiO<sub>2</sub> substrates for quantitative evaluation of the surface linker functionalization efficiencies via fluorescence microscopy. To fabricate the PMMA micro-patterns, we utilize a similar protocol as described for TiO<sub>2</sub> nanocylinders (**Methods**). The main differences include spin-coating PMMA 950k A11 to achieve a ~1.9 μm-thick layer and altered e-beam settings (a current of 312 nA, a diameter of 300 nm through defocusing the beam, and a dose of 1000 μC/cm<sup>2</sup>). For the quartz SiO<sub>2</sub> substrates (X-cut, University Wafer, USA) alone, we sputter a 30 nm-thick gold (Au) layer (EM ACE600, Leica, The Netherlands) onto the spin-coated PMMA layer to prevent charging. Following e-beam patterning, we remove the Au layer by a wet etchant (TFA, Transene, USA). As described in **Methods**, we treat the micro-patterned substrates with O<sub>2</sub> plasma (Plasma-PREEN I) prior to the functionalization process.

For the evaluation of the surface functionalization efficiencies of the different linkers to single-crystal TiO<sub>2</sub> (and SiO<sub>2</sub>) substrates, we use amino and NHS-ester modified fluorophores (ATTO 647N, ATTO-TEC GmbH, Germany). They are covalently added to the organic functional groups of the surface linkers employed. For the substrates coated with ETA, APDMES, and BADMSCP, we dissolve NHS-ester labeled fluorophores in PBS buffer (pH 8.4, Sigma-Aldrich, The Netherlands) to a final concentration of 10 μM and add to the functionalized surfaces. After the reaction time of 1 h, we wash the substrates three times each with PBS/TWEEN® buffer (pH 7.4) and DI water to remove residual physisorbed molecules, and dry under a N<sub>2</sub> stream. For GPDMS-coated and PEGylated surfaces, we add 10 μM of amino-labeled fluorophores to PBS buffer (pH 7.4) and MES/EDC buffer (100 mM MES (pH 4.7) containing 50 mM EDC (1-Ethyl-3-(3-dimethylaminopropyl)carbodiimid, Sigma-Aldrich, The Netherlands)), respectively, and the fluorophore coupling reactions take place for 1 h. We wash the substrates with PBS/TWEEN® buffer (pH 7.4) and DI water, followed by drying under a N<sub>2</sub> stream, as stated before.

We perform the fluorescence measurements of the functionalized surfaces and nanocylinders using an epifluorescence microscope (IX-81, Olympus, The Netherlands) equipped with a Peltier-cooled back-illuminated electron multiplying charge coupled device (EMCCD) camera (IXON, 512 × 512 pixels, Andor, Ireland), in combination with an oil-immersion objective lens (100×/NA1.3, UPLNFLN, Olympus, The Netherlands). The fluorophores are excited using a diode laser (λ = 640 nm, Cell Laser System, Olympus, The Netherlands). For quantitative measurements, we measure the fluorescence intensity (in photon counts per second) of an area of 12.5 × 12.5 μm<sup>2</sup> for different square micro-patterns on each sample. We calculate the average intensity – normalized to the area of 1 μm<sup>2</sup> – and the corresponding standard deviations to compare the different linker molecule coverages (**Fig. S5†**).

### **Preparation of DNA construct for OTW experiments**

We carry out the DNA extension and supercoiling measurements (**Fig. 5**) on a linear 21.8 kbp DNA that contains biotin and digoxigenin modified nucleotides (biotin-16-dUTP and digoxigenin-11-dUTP, respectively, Roche Diagnostics, The Netherlands) at the opposite extremities (600 bp each). We prepare the DNA by ligating the biotin- and digoxigenin-enriched handles to a 20.6 kbp DNA fragment that is obtained via a *NotI/XhoI* digestion of Supercos1-lambda 1,2 plasmid (Agilent Technologies, USA). We create the DNA handles by PCR amplification of a 1.2 kbp fragment from pBlueScript II SK+ (Agilent Technologies, USA) using the primers – 5'-GACCGAGATAGGGTTGAGTG and 5'-CAGGGTCGGAACAGGAGAGC – in the presence of either biotin-16-dUTP or digoxigenin-11-dUTP. Prior to ligation using T4 DNA ligase (New England Biolabs, UK), the biotin and digoxigenin containing handles are digested with *NotI* and *XhoI*, respectively.<sup>9</sup>

### **Preparation of flow cell for OTW experiments**

We perform OTW experiments (**Fig. 5**) in a custom-made flow cell assembled from two 24 × 60 mm<sup>2</sup> borosilicate coverslips (#1.5, ~170 μm thickness, Menzel GmbH, Germany) separated by a single-layer Parafilm<sup>®</sup> (Sigma-Aldrich, The Netherlands) spacer.<sup>1,8,10</sup> We drill two holes of ~1 mm diameter in the top coverslips using a sand blaster, to connect with inlet and outlet tubings. Prior to flow cell assembly, we clean the coverslips using a 4% (v/v) aqueous Hellmanex<sup>®</sup> III (Hellma GmbH, Germany) solution and then DI water, in both cases by sonication for 20 min at 40 °C. We dry the cleaned coverslips under a N<sub>2</sub> stream. For the bottom coverslips, we perform surface functionalization to attach biomolecules. To increase the density of surface hydroxyl groups, which allows for denser, more homogeneous functionalization, we treat the bottom coverslips with O<sub>2</sub> plasma (Plasma-PREEN I) for 1 min with O<sub>2</sub> flow rate of 3 scfh and RF power of 200 W. We incubate these coverslips in DMSO solution containing 5 M ETA for 12 h at room temperature. Afterwards, we wash the functionalized coverslips thoroughly with DI water and dry them under a N<sub>2</sub> stream. Single-layer Parafilm<sup>®</sup> spacers are prepared by cutting out the desired flow cell channel shape, which is properly aligned to the holes in the top coverslips. Finally, we assemble the flow cells and seal the channels by melting the Parafilm<sup>®</sup> spacers between the coverslips on a hotplate for 30 s at 90 °C.

### **Bioconjugation of DNA to single-crystal TiO<sub>2</sub> nanocylinders for OTW experiments**

In an OTW, we are able to carry out the extension and coiling measurements on individual, torsionally constrained DNA molecules.<sup>1-5</sup> We tether the DNA molecules to the bottom surface of the flow cell channel via digoxigenin:anti-digoxigenin coupling and to the functionalized single-crystal rutile TiO<sub>2</sub> nanocylinders via biotin:streptavidin coupling (**Fig. 5a**). To do so, we perform three steps. First, we PEGylate the ETA-coated flow cell channel both to covalently attach digoxigenin antibodies and to ensure an effective surface passivation against non-specific physisorption of streptavidin-coated TiO<sub>2</sub> nanocylinders. We achieve this by incubating the channel with 2 mM PEG dissolved in 100 mM MES buffer (pH 4.7) for 1 h. After washing with DI water, we incubate for 1 h with 8 μM digoxigenin IgG antibodies (Roche Diagnostics, The Netherlands) dissolved in MES/EDC buffer (pH 4.7). We wash the channel with PBS buffer (pH 7.4) and incubate BlockAid™ (Life

Technologies, USA) for 1 h for additional surface passivation. Subsequently, we wash the channel with PBS buffer (pH 7.4). Second, we attach individual DNA molecules via the digoxigenin handles to the digoxigenin antibody-covered flow cell channel by incubating 5 pM of DNA for 1 h. We remove non-specifically adhered DNA molecules by washing the channel with PBS buffer (pH 7.4). Third, we attach the DNA via the biotinylated handles to the streptavidin-coated TiO<sub>2</sub> nanocylinders (**Methods**) by incubating them in the flow cell channel for ~30 min. We remove non-attached nanocylinders by flushing 1:1 diluted (v/v) BlockAid™ in PBS/Triton™ buffer (pH 7.4). We perform all DNA extension and coiling measurements in PBS/Triton™ buffer.

### **OTW instrumentation and DNA measurements with single-crystal TiO<sub>2</sub> nanocylinders**

For optical trapping of single-crystal TiO<sub>2</sub> nanocylinders in our OTW setup (**Fig. 5b,c**), we expand and collimate a linearly polarized laser ( $\lambda = 1064$  nm, Compass CW 1064-4000M, Coherent, The Netherlands) beam using a beam expander (4401-181-000-20, LINOS, Germany) to fill properly the input aperture of an objective lens (60 $\times$ /NA1.2, CFI-PLAN-APO-VC-60XA-WI, Nikon, The Netherlands). The power entering the objective lens is always set to 100 mW during experiments. The objective lens focuses the laser beam into a flow cell, generating an optical trap.

To calibrate the optical trap, we monitor the fluctuations of an isolated, optically trapped TiO<sub>2</sub> nanocylinder using a position-sensitive detector (PSD) (DL100-7PCBA3, Pacific Silicon Sensor, The Netherlands) that acquires at 100 kHz (**Fig. S7†**). The nanocylinder trapping position is ~7  $\mu$ m above from the bottom surface of the flow cell channel, to conserve the similar measurement conditions with the case of DNA-tethered nanocylinders.<sup>11</sup> We can calculate the restoring force acting on a nanocylinder displaced from the trap center, by multiplying the measured displacement with the calibrated trap stiffness. Precise linear translation of the flow cell is possible using a piezo-actuator (P-517.3CD, Physik Instrumente, Germany) in x, y, and z directions.

For the force-induced DNA-extension experiments, we move the flow cell along the axis of laser beam propagation (axial direction) at a constant speed (~1  $\mu$ m/s) while maintaining the laser beam at a fixed position. As the flow cell moves away from the laser beam focus, the increased DNA-tethered nanocylinder's displacement from the trap center induces higher axial force to the DNA molecule. For the DNA coiling experiments, a constant axial force should be applied to the trapped, DNA-tethered nanocylinder since whether the DNA twists or forms plectonemic supercoils strongly influenced by the tension applied to the molecule.<sup>12</sup> We use a feedback loop between the piezo-actuator and PSD to clamp the axial force at the specified setpoint. By simultaneously rotating the linear input polarization of the laser beam, we apply torque to the TiO<sub>2</sub> nanocylinder, coiling the DNA molecule. The polarization can be rotated either by manual rotation of a half-wave plate (PWPS-1064-10-2, CVI Melles Griot, Germany), or by a fast electro-optical modulator (EOM) (LM 0202-LT, LINOS, Germany) in combination with quarter-wave plates (PWPS-1064-10-4, CVI Melles Griot, Germany).

## Supplementary Tables

**Table S1.** Dry etching conditions for single-crystal TiO<sub>2</sub> during optimization of the CHF<sub>3</sub>-RIE process.<sup>a)</sup>

Sample	CHF <sub>3</sub> flow [sccm]	O <sub>2</sub> flow [sccm]	Ar flow [sccm]	RF power [W]	Chamber pressure [μbar]	TiO <sub>2</sub> etch rate [nm/min]	Cr etch rate [nm/min]	Etch selectivity [TiO <sub>2</sub> :Cr]
Ra1	50	5	30	200	50	68	3.7	18
Ra2	50	5	30	<b>165</b>	50	58	3.2	18
Ra3	50	5	30	<b>100</b>	50	30	1.7	18
Ra4	50	5	30	200	<b>10</b>	30	8.3	4
Rb1	50	5	30	200	50	77	4.1	19
Rb2	50	5	<b>0</b>	200	50	73	3.5	21

<sup>a)</sup>The bold red numbers denote altered process parameters compared to the reference samples (Ra1 and Rb1).

### Dry etching conditions for single-crystal TiO<sub>2</sub> during optimization of the CHF<sub>3</sub>-RIE process

We show the representative etching conditions (**Table S1†**) used during optimization of the CHF<sub>3</sub>-based plasma etching of single-crystal TiO<sub>2</sub> in an RIE system. Throughout the optimization, we fix the flow rate of CHF<sub>3</sub> gas, the main etchant, at the maximum value of 50 sccm, and set the flow rate of O<sub>2</sub> gas at 5 sccm which is the median value of our target range (0–10 sccm). More accurate comparisons are possible within the same batches of the applied Cr etch mask, designated as Ra (H: 100 nm, D: 535 nm) and Rb (H: 100 nm, D: 345 nm). The samples Ra1 and Rb1 are the reference samples, while the other samples differ by a single process parameter (designated as bold red numbers in **Table S1†**).

As an elevated RF power increases the etch rates of TiO<sub>2</sub> while maintaining nearly constant etch selectivity (compare samples Ra1, Ra2, and Ra3 in **Table S1†**), we select the highest available power (200 W). We find that an increase in the chamber pressure (from 10 to 50 μbar) enhances the etch selectivity by increasing the TiO<sub>2</sub> etch rates and decreasing the Cr etch rates (compare samples Ra1 and Ra4 in **Table S1†**). However, we do not utilize chamber pressures exceeding 50 μbar, as higher values result in excessive deposition of fluorocarbon passivation layers<sup>13</sup> that are sufficiently thick to reduce the TiO<sub>2</sub> etch rates again. With these parameters fixed, we vary the gas composition. The addition of Ar gas, which results in harsher physical etching by heavy ions, generally increases etch rates.<sup>14</sup> Indeed, upon its addition (at 30 sccm) both the Cr and TiO<sub>2</sub> etch rates are increased; however, as the increase in the Cr etch rate surpasses that of TiO<sub>2</sub>, a deteriorated etch selectivity results (compare samples Rb1 and Rb2 in **Table S1†**). Our optimized process condition thus consists of CHF<sub>3</sub> at 50 sccm, a chamber pressure of 50 μbar, and an RF power of 200 W. With these fixed parameters, we vary O<sub>2</sub> gas flow rate from 0 sccm to 10 sccm to control sidewall profiles (**Fig. S3†**), and vertical sidewall can be obtained with 0.5 sccm of O<sub>2</sub>.



**Table S2.** Dry etching conditions for single-crystal TiO<sub>2</sub> nanofabrication.<sup>a)</sup>

Figure	Etching System	Etching conditions
Fig. 2a	F1	Cr etch mask (H: 45 nm, D: 175 nm), <b>CHF<sub>3</sub></b> :O <sub>2</sub> = 50:0.5 sccm, RF 200 W, chamber pressure 50 μbar, DC bias -950 V, etch time 11 min ( <b>optimized</b> ).
Fig. 2b	F2	Cr etch mask (H: 100 nm, D: 255 nm), <b>CHF<sub>3</sub></b> :O <sub>2</sub> = 50:8 sccm, RF 200 W, chamber pressure 50 μbar, DC bias -1100 V, etch time 15 min ( <b>optimized</b> ).
Fig. 2c	F1	Cr etch mask (H: 100 nm, D: 535 nm), <b>CHF<sub>3</sub></b> :O <sub>2</sub> :Ar = 50:5:30 sccm, RF 165 W, chamber pressure 50 μbar, DC bias -855 V, etch time 15 min.
Fig. 2d	F3	Cr etch mask (H: 100 nm, D: 535 nm), <b>SF<sub>6</sub></b> :CH <sub>4</sub> :Ar = 15:30:50 sccm, ICP:RF = 2500:300 W, chamber pressure 30 μbar, DC bias -50 V, etch time 10 min, sample holder temperature 0 °C, chamber temperature 200 °C.
Fig. 2e	F4	Cr etch mask (H: 130 nm, D: 185 nm), <b>SF<sub>6</sub></b> :He = 50:100 sccm, ICP:RF = 800:200 W, chamber pressure 50 μbar, DC bias -475 V, etch time 12 min, chamber temperature 25 °C.
Fig. 2f	F4	Cr etch mask (H: 120 nm, D: 205 nm), <b>SF<sub>6</sub></b> :He = 20:100 sccm, ICP:RF = 300:300 W, chamber pressure 100 μbar, DC bias -835 V, etch time 4 min, chamber temperature 25 °C ( <b>optimized</b> ).
Fig. 3	F2	Cr etch mask (H: 60 nm, D: 220 nm), <b>CHF<sub>3</sub></b> :O <sub>2</sub> = 50:4 sccm, RF 200 W, chamber pressure 50 μbar, DC bias -1100 V, etch time 15 min ( <b>optimized</b> ).
Fig. 5	F4	Cr etch mask, the same etching condition as Fig. 2f ( <b>SF<sub>6</sub></b> ).
Fig. S2†	F3	Various etch mask materials, <b>SF<sub>6</sub></b> :CH <sub>4</sub> :Ar = 15:30:50 sccm, ICP:RF = 1500:250 W, chamber pressure 30 μbar, DC bias -55 V, etch time 10 min, sample holder temperature 0 °C, chamber temperature 200 °C.
Fig. S3†	F1	Cr etch mask (H: 100 nm, D: 345 nm), the same etching condition as Fig. 2a ( <b>CHF<sub>3</sub></b> ), except for the etch time (15 min) and the O <sub>2</sub> gas flow rate (0, 0.5, 1, 5, or 10 sccm).
Fig. S4†	F2	Cr etch mask (H: 30 nm, D: 190 nm), the same etching condition as Fig. 3 ( <b>CHF<sub>3</sub></b> ), except for the etch time (8 min).
Fig. S7†	F4	Cr etch mask, the same etching condition as Fig. 2f ( <b>SF<sub>6</sub></b> ).

<sup>a)</sup>The bold red letters denote the main etchant gas in each condition.

### Dry etching conditions for single-crystal TiO<sub>2</sub> nanofabrication

We use etching systems that are denoted as F1 (Fluor Z401S, Leybold Heraeus, Germany), F2 (Fluor Z401S, Leybold Heraeus, Germany), F3 (AMS100 I-speeder, Adixen, France), and F4 (Plasmalab System 100, Oxford Instr., UK). The F1 and F2 are two nominally identical RIE systems, while F3 and F4 are two distinct ICP-RIE systems. We summarize the etching conditions for each batch of TiO<sub>2</sub> nanocylinders in Table S2†.

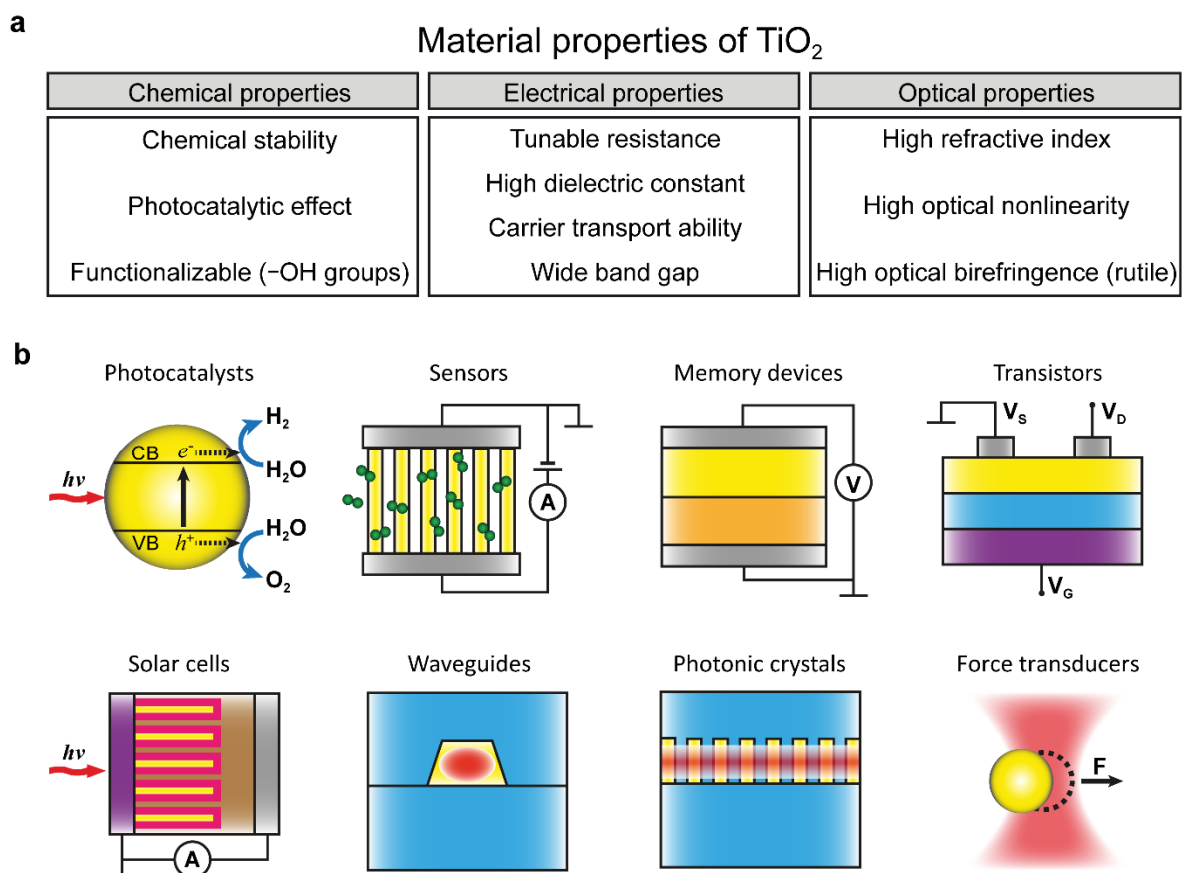
**Table S3.** Dimensional analysis of high and low aspect-ratio TiO<sub>2</sub> nanocylinders.

Sample	Statistical parameter	Top diameter	Bottom diameter	Height	Top roundness	Bottom roundness	Volume
<b>Fig. 3</b> (15 min etch)	Average	151 nm	215 nm	652 nm	0.97	0.98	0.017 $\mu\text{m}^3$
	Local RSD	4.4%	2.3%	0.6%	1.0%	0.5%	4.5%
	Global RSD	4.7%	2.7%	1.4%	1.1%	0.5%	5.2%
<b>Fig. S4†</b> (8 min etch)	Average	149 nm	187 nm	273 nm	0.98	0.99	0.006 $\mu\text{m}^3$
	Local RSD	1.5%	0.9%	1.3%	0.5%	0.3%	2.1%
	Global RSD	2.4%	1.7%	3.1%	0.6%	0.4%	4.1%

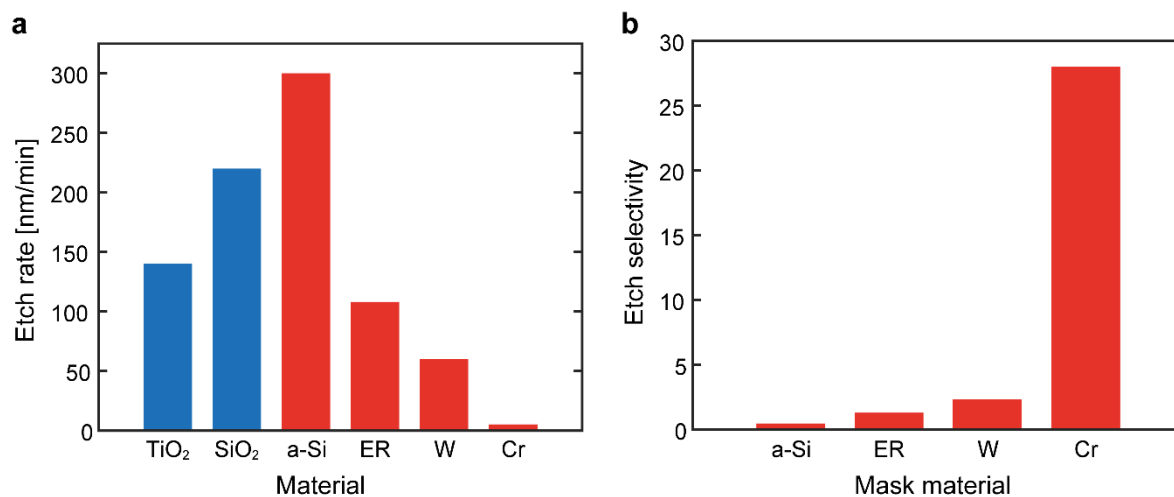
#### Dimensional analysis of high and low aspect-ratio TiO<sub>2</sub> nanocylinders

We have analyzed SEM images of high and low aspect-ratio nanocylinder batches to quantify both the local and global structural uniformity. We summarize the obtained statistical parameters for each batch of TiO<sub>2</sub> nanocylinders in **Table S3†**, and present the corresponding graphs in **Fig. 3d-f** (high aspect-ratio: 3.6) and **Fig. S4d-i†** (low aspect-ratio: 1.6).

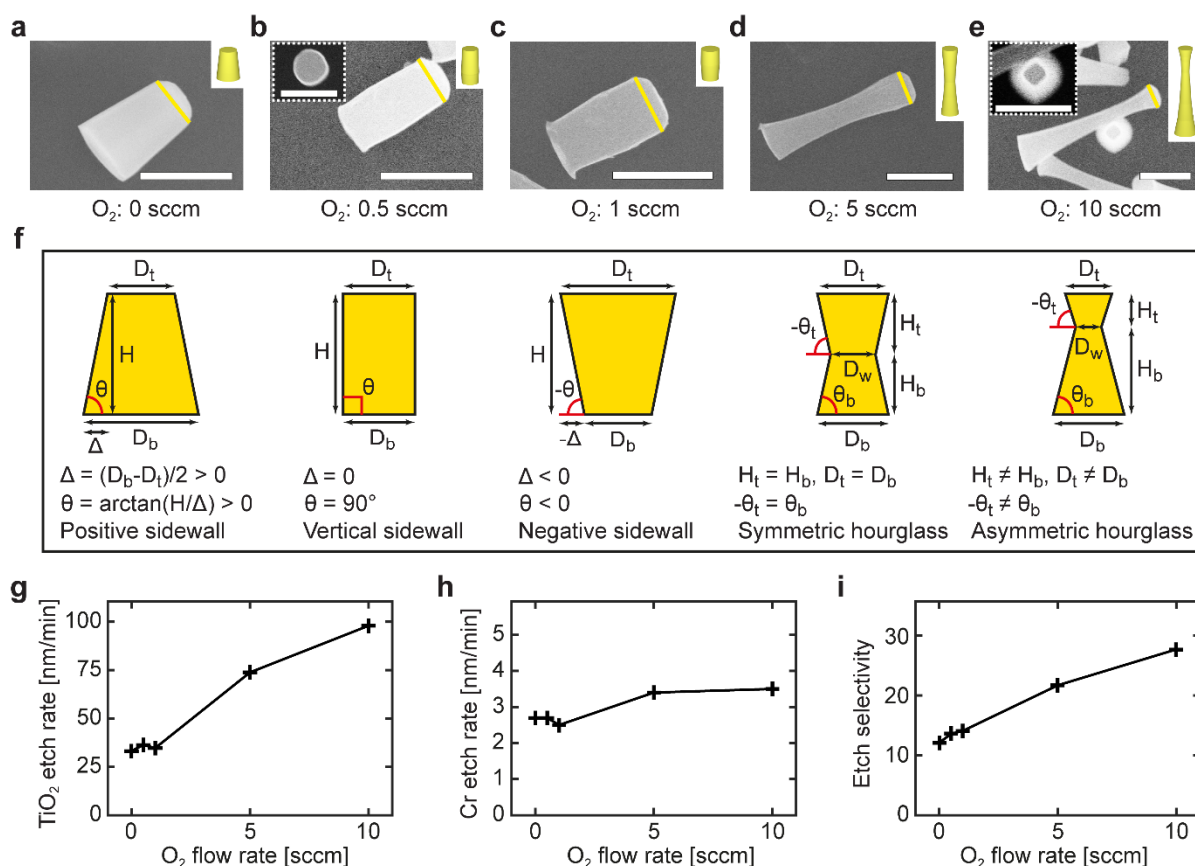
## Supplementary Figures



**Fig. S1.** Diverse applications of TiO<sub>2</sub> at the nanoscale. **(a)** Overview of the chemical, electrical, and optical properties that make TiO<sub>2</sub> a versatile material for different applications. **(b)** Illustrations of nanoscale applications of TiO<sub>2</sub> (yellow). Top, left to right: a TiO<sub>2</sub> nanoparticle serves as a photocatalyst for water splitting into oxygen and hydrogen gases ( $h\nu$ : input radiation energy, CB: conduction band, VB: valence band,  $e^-$ : electron,  $h^+$ : hole); a TiO<sub>2</sub> nanopillar array acts as a gas sensor (gray: metal electrodes, green: gas molecules, A: current as a sensing signal); a TiO<sub>2</sub> thin film acts as a tunable resistance material in a resistive random access memory device (gray: metal electrodes, orange: TiO<sub>2-x</sub>, V: voltage as a read/write signal); a TiO<sub>2</sub> thin film can be used as a channel layer in a transparent transistor (gray: metal electrodes, blue: gate insulator, purple: transparent electrode,  $V_s$ ,  $V_d$ , and  $V_g$  denote voltages at source, drain, and gate terminals, respectively). Bottom, left to right: a TiO<sub>2</sub> nanorod array acts as a photoanode in a solar cell ( $h\nu$ : radiation energy from the sun, gray: metal electrode, purple: transparent electrode, magenta: sensitization layer e.g. dye molecules or quantum dots, brown: electrolyte, A: current as converted energy); a nanostructured TiO<sub>2</sub> forms the core of a strip waveguide to support lightwave propagation (blue: cladding layers, red: confined lightwave); a two-dimensional TiO<sub>2</sub> photonic crystal slab used to manipulate the flow of lightwave (blue: cladding layers, red: confined lightwave); an optically trapped TiO<sub>2</sub> nanoparticle used as a force transducer (red: focused laser beam, dotted circle: trap center, F: force induced by the displacement of the nanoparticle).



**Fig. S2.** The etch rates and etch selectivities of different mask materials. **(a)** The etch rates for substrate (blue bars) materials (TiO<sub>2</sub>: (100)-cut rutile single crystal, ~140 nm/min; SiO<sub>2</sub>: X-cut quartz single crystal, ~220 nm/min) and mask (red bars) materials (a-Si: amorphous silicon layer deposited by a plasma-enhanced chemical vapor deposition system (Plasmalab 80 Plus, Oxford Instr., UK), ~300 nm/min; ER: spin-coated and baked e-beam resist layer (NEB-22A2E, Sumitomo Chemical, Belgium), ~110 nm/min; W: tungsten layer deposited by an e-beam evaporator (Temescal FC-2000, Ferrotec, Germany), ~60 nm/min; Cr: chromium layer deposited by the same evaporator, ~5 nm/min). All results are obtained under the same dry etching conditions (using the F3 etching system; etching conditions in **Table S2†**). **(b)** Etch selectivity of each mask material for single-crystal TiO<sub>2</sub> dry etching, which is the etch rate of TiO<sub>2</sub> divided by that of the mask material (a-Si: 0.5, ER: 1.3, W: 2.3, Cr: 28).



**Fig. S3.** Control of sidewall profiles and etch characteristics in single-crystal TiO<sub>2</sub> nanocylinders by variation of O<sub>2</sub> flow rate in the CHF<sub>3</sub>-RIE process. **(a-e)** SEM images of single-crystal TiO<sub>2</sub> nanocylinders produced under identical etching conditions (using the F1 etching system; etching conditions in **Table S2†**) apart from the O<sub>2</sub> flow rate (values shown at the bottom of each image). Scale bars denote 500 nm. Top surfaces of the nanocylinders are marked with yellow lines because the remaining Cr masks are also visible in these images. The insets in top-right corner illustrate (to scale) the corresponding three-dimensional shapes of the nanocylinder SEM images. The types of obtained nanocylinder shapes include **(a)** positive sidewall angles, **(b)** vertical sidewall angles, **(c)** negative sidewall angles, **(d)** symmetric hourglass shapes, and **(e)** asymmetric hourglass shapes. In **(b)** and **(e)**, the insets in top-left corner (scale bars denote 500 nm) show top-view SEM images of nanocylinders cut at their middle, displaying cross-sections that are **(b)** circular or **(e)** diamond-shaped. **(f)** For the analysis of sidewall angles ( $\theta$ ), we use two-dimensional models as defined here. The definition of sidewall angles is illustrated for the cases of positive, vertical, and negative angles, using the measured heights ( $H$ ) and diameters of top ( $D_t$ ) and bottom ( $D_b$ ). The hourglass-shaped nanocylinders possess two sidewall angles and heights for both top ( $\theta_t$ ,  $H_t$ ) and bottom ( $\theta_b$ ,  $H_b$ ) sides, and an additional waist diameter ( $D_w$ ). **(g-i)** The etch characteristics are shown as a function of the O<sub>2</sub> flow rate: the etch rates of **(g)** TiO<sub>2</sub>, **(h)** Cr, and **(i)** the resulting etch selectivities (TiO<sub>2</sub>:Cr). The measured dimensions extracted from the SEM images **(a-e)** are as follows: **(a)**  $D_t$ : 285 nm,  $D_b$ : 395 nm,  $H$ : 500 nm,  $\theta$ : 84°; **(b)**  $D_t = D_b$ : 275 nm,  $H$ : 545,  $\theta$ : 90°; **(c)**  $D_t$ : 305 nm,  $D_b$ : 260 nm,  $H$ : 520 nm,  $\theta$ : -88°; **(d)**  $D_t = D_b$ : 260 nm,  $D_w$ : 175 nm,  $H_t = H_b$ : 555 nm,  $-\theta_t = \theta_b$ : 86°; **(e)**  $D_t$ : 245 nm,  $D_b$ : 370 nm,  $D_w$ : 135 nm,  $H_t$ : 385 nm,  $H_b$ : 1085 nm,  $\theta_t$ : -82°,  $\theta_b$ : 84°.

#### Control mechanism for sidewall profiles in CHF<sub>3</sub>-etched single-crystal TiO<sub>2</sub> nanocylinders

We observe that tuning the O<sub>2</sub> flow rate during the single-crystal TiO<sub>2</sub> etching process allows us to control the sidewall profile of the nanostructures. We attribute the formation of different sidewall profiles (positive, vertical, negative, and hourglass-shaped) to underlying changes in the thickness of a sidewall passivation layer that result from the interplay between CHF<sub>3</sub> and O<sub>2</sub> plasma. The thickness variation permits both the formation

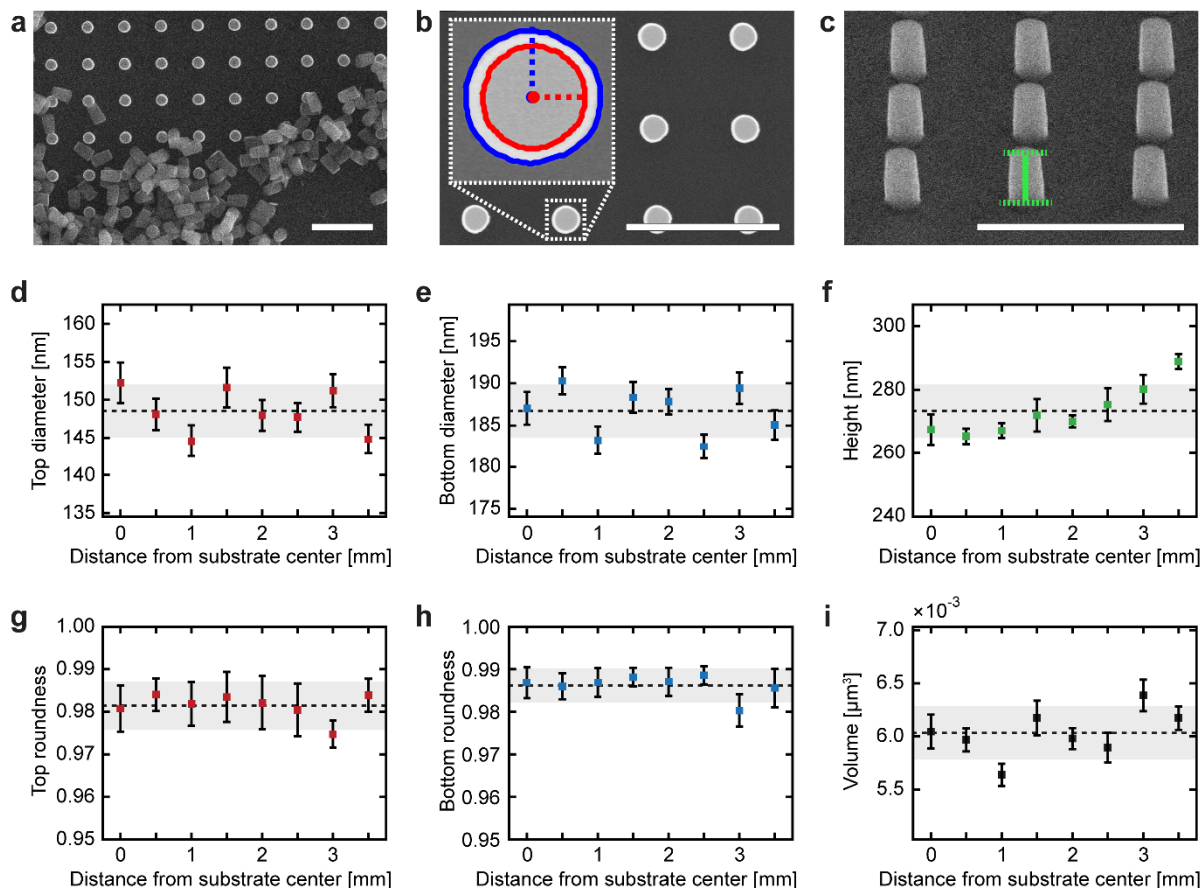
of positive sidewall angles in the absence of O<sub>2</sub> flow and the formation of vertical (or negative) sidewall angles at an O<sub>2</sub> flow of 0.5 (1.0) sccm (**Fig. S3a-c†**). The hourglass-shaped etch profiles likely result from substantially reduced TiO<sub>2</sub> surface passivation combined with the random trajectories of reactive ions<sup>15,16</sup> (**Fig. S3d,e†**).

### **Control mechanism for cross-sectional shapes and etch selectivity in CHF<sub>3</sub>-etched single-crystal TiO<sub>2</sub> nanocylinders**

We find that the single-crystal TiO<sub>2</sub> nanocylinders etched at low O<sub>2</sub> flow rates (0–1 sccm) exhibit circular cross-sections (**Fig. S3b†**, **inset** in top-left corner), while those etched at high O<sub>2</sub> flow rates (5–10 sccm) feature diamond-shaped cross-sections (**Fig. S3e†**, **inset** in top-left corner). These differences may result from changes in the predominant etching mode: at low O<sub>2</sub> flow rates, the initial shape of the etch masks (circular in the case of **Fig. S3†**) should be directly transferred to the etched nanostructures, as the dominance of physical etching by ion bombardment results in the same etch rate independently of crystallographic orientation; conversely, at high O<sub>2</sub> flow rates, chemical etching may predominate than physical etching, resulting in etch rates that vary per orientation of the crystal planes in the single-crystal TiO<sub>2</sub> substrates.<sup>17</sup> Moreover, the above reasoning is supported by the fact that TiO<sub>2</sub> etch rates (**Fig. S3g†**) increase significantly (~3-fold) while Cr etch rates (**Fig. S3h†**) remain nearly the constant (~3 nm/min), as we increase O<sub>2</sub> flow rate. The removal of Cr mask layer is possible only by the physical etching but not by the chemical etching based on fluorine chemistry while both etching modes induce TiO<sub>2</sub> etching. We attribute this to a decreased thickness of the CHF<sub>3</sub> plasma-generated fluorocarbon passivation layer on TiO<sub>2</sub> surfaces in the presence of O<sub>2</sub> plasma.<sup>18</sup> As such a layer protects TiO<sub>2</sub> surfaces from chemical reaction with etching species, its decreased thickness results in an increase of the TiO<sub>2</sub> etch rates whilst those of Cr remain nearly unaffected, enhancing etch selectivity (**Fig. S3i†**).

### **The reproducibility of different sidewall profiles in CHF<sub>3</sub>-etched single-crystal TiO<sub>2</sub> nanocylinders**

A repetition of this experiment in the second nominally identical RIE system yields the similar trends but at slightly altered O<sub>2</sub> flow rates (using the F2 etching system; etching conditions in **Table S2†**). For example, etching nanocylinders with vertical sidewall angles requires an O<sub>2</sub> flow rate of 4–8 sccm (compared to ~0.5 sccm in the first RIE system (**Fig. S3b†**)). Similarly, etching nanocylinders into hourglass-shapes requires an O<sub>2</sub> flow rate of ~16 sccm (compared to 5–10 sccm in the first RIE system (**Fig. S3d,e†**)). We attribute this discrepancies in parameters to the differences in instrument calibration, e.g. of the mass flow controllers for the control and measurement of O<sub>2</sub> flow rates.



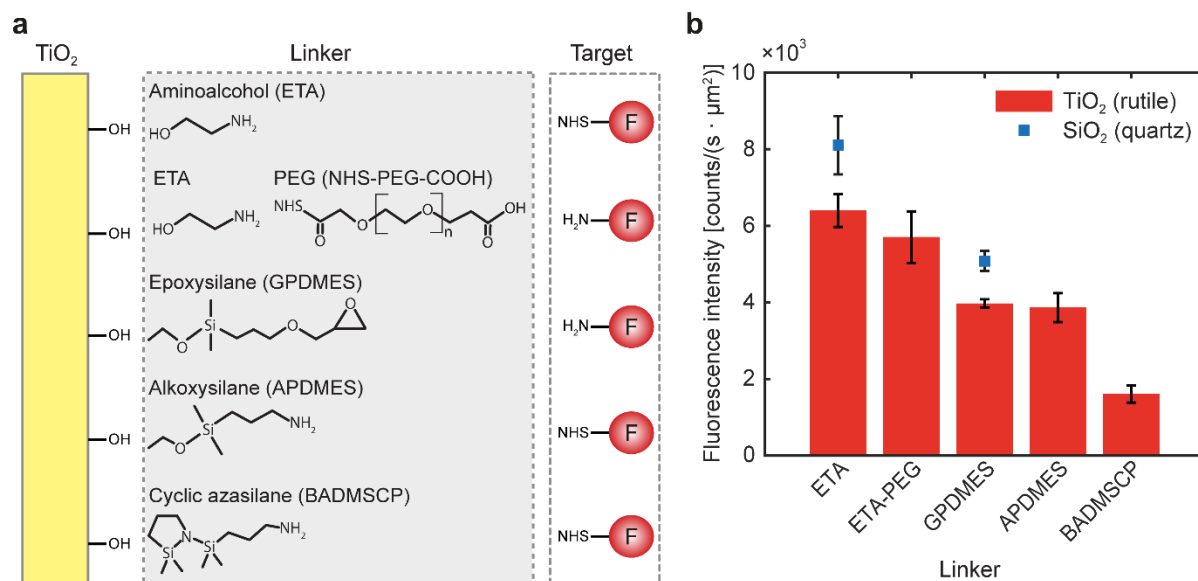
**Fig. S4.** Dimensions of fabricated single-crystal  $\text{TiO}_2$  nanocylinders. **(a-c)** SEM images of etched single-crystal  $\text{TiO}_2$  nanocylinders (light gray). Scale bars denote 1  $\mu\text{m}$ . **(a)** Top-view of a single-crystal  $\text{TiO}_2$  substrate with partially cleaved nanocylinders. An array of rigidly fixed nanocylinders is visible in the top left corner, and the cleaved substrate surface is bottom right corner. The released nanocylinders are positioned at the interface of these regions. **(b)** Top-view of a substrate with etched nanocylinders. The inset shows a zoom-in as an example for image analysis. The red (blue) contour, dotted line, and dot represent the boundary, equivalent radius, and center of nanocylinder top (bottom) surface, respectively. **(c)** Tilted-view ( $60^\circ$ ) of a substrate with etched nanocylinders. The green dotted horizontal lines are crossing the centers of top and bottom surfaces, and the green vertical line indicates the height that will be converted to the actual height considering the tilting angle. **(d-i)** Nanocylinder dimensions extracted from the SEM images. The graphs display the **(d)** top diameter, **(e)** bottom diameter, **(f)** height, **(g)** top roundness, **(h)** bottom roundness, and **(i)** volume as a function of the radial distance from the substrate center. The roundness (defined as  $4\pi A/P^2$ , A: area, P: perimeter) measures how closely the shape of a nanocylinder's cross section resembles that of a circle, where 1 corresponds to a perfect circle and smaller values imply deviations from circular. Measurement points are spaced by 0.5 mm from the center of the substrate to its edge. At each point, the diameters (heights) are calculated from  $n = 12$  ( $n = 10$ ) different nanocylinders. The square markers and the error bars in the graphs represent the mean and the standard deviation of the local uniformity, respectively. The horizontal dotted black lines and the top and bottom sides of the gray shaded boxes in the graphs represent the mean and the standard deviation of the global uniformity, respectively.

#### Distributions of fabricated single-crystal $\text{TiO}_2$ nanocylinder dimensions

The comparison between single-crystal  $\text{TiO}_2$  nanocylinder dimensions presented in **Fig. S4**<sup>†</sup> and those presented earlier (**Fig. 3**) provides more information for the analysis of the nanocylinder dimensions. We etch the different batches of nanocylinders under the same conditions, except for the etch duration (**Table S2**<sup>†</sup>). The etch time of the nanocylinders analyzed in **Fig. S4**<sup>†</sup> (8 min) is approximately twice less than that of the

nanocylinders shown in **Fig. 3** (15 min). Both etch times demonstrate a similar trend regarding the nanocylinder dimensions (analysis results are summarized in **Table S3†**). The observed irregular Cr mask erosion effect, which depends on the roughness of the mask surface, causes stronger deformation of the top surface geometry than the bottom of the nanocylinders; we expect that the bottom surface geometry is mostly determined by the initial round shape of etch mask while the top surface geometry is the same as the eroded etch mask until the end of the etching process. This geometry deformation is also observable in the roundness analysis, in which the top roundness values are smaller than the bottom roundness values for both batches of nanocylinders. For this reason, the top diameters show less local uniformity than the bottom diameters. As this effect is more profound for extended etch times, etch time of 15 min results in less local uniformity than etch time of 8 min for both top and bottom diameters. For each measurement point, the top and bottom diameters are directly correlated as observable in **Fig. S4†** and **Fig. 3**. However, variations in the top and bottom diameters across a substrate are random, possibly due to the instability of e-beam size or current during e-beam patterning process. Regardless of these variations, the top and bottom diameters exhibit still high global uniformity for both batches of nanocylinders (RSD  $\leq 5\%$ ), which lie in the same order of magnitude as their local uniformity. Further, we observe high global uniformity in nanocylinder heights across the substrates (RSD  $\leq 3\%$ ) regardless of the loading effect. These excellent global uniformity in both diameters and heights leads to nanocylinder volumes with high global uniformity (RSD  $\leq 5\%$ ) across a substrate which is desirable for the application of torque in an OTW.<sup>1</sup>

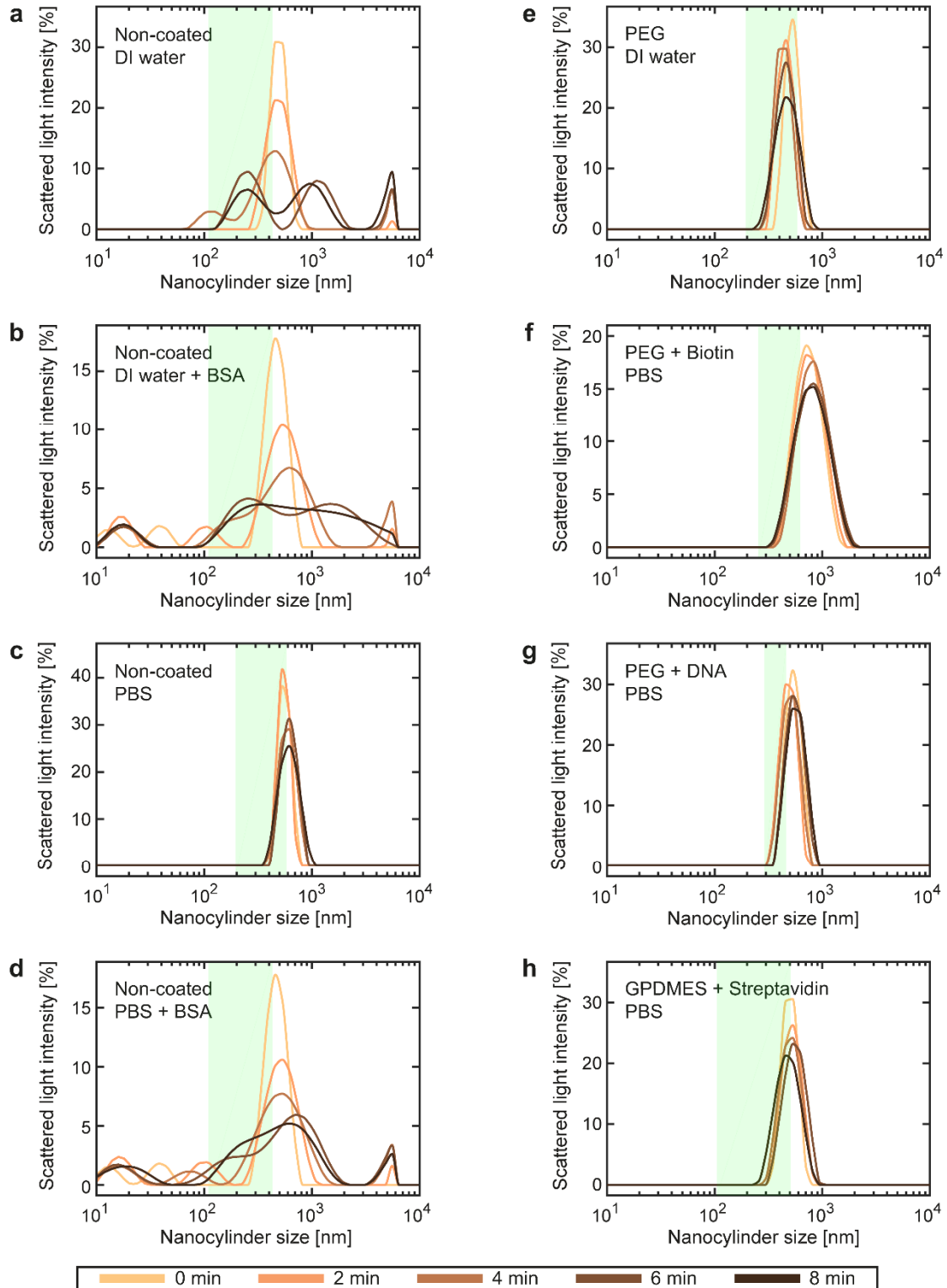




**Fig. S5.** Quantitative comparison of surface functionalization efficiencies on single-crystal TiO<sub>2</sub> for different linker molecules. **(a)** Schematic of the different functionalization strategies. At left, the TiO<sub>2</sub> (or other oxide materials, e.g. SiO<sub>2</sub>) surface provides hydroxyl groups (-OH) to which the linkers bind covalently. In the center, the used linker molecules (ETA, GPDMEs, APDMES, and BADMSCP) are shown with their molecular structures, including the PEGylation of ETA-coated surface. At right, target molecules are NHS-ester or amine modified ATTO 647N fluorophores (F), binding to the different functional group of each linker (ESI Methods†). The fluorophores allow quantitative measurements via fluorescence microscopy. However, in the same manner, other organic molecules, such as biomolecules or polymers, can be bound to the surface linkers. **(b)** Quantitative comparison of differently functionalized single-crystal rutile TiO<sub>2</sub> (red bars) and quartz SiO<sub>2</sub> (blue squares) substrates. The measured fluorescence intensity represents the surface coating density while the error bar (standard deviation) reflects the homogeneity of the coatings (ESI Methods†).

### Comparison of TiO<sub>2</sub> and SiO<sub>2</sub> in surface functionalization efficiency

It is known that TiO<sub>2</sub> has lower functionalization efficiency compared to other widely used oxide materials, e.g. SiO<sub>2</sub> and Al<sub>2</sub>O<sub>3</sub>.<sup>19,20</sup> To quantify this difference in functionalization efficiency, we compare the surface coating efficiency of TiO<sub>2</sub> (rutile) with that of SiO<sub>2</sub> (quartz). We select two linkers for this comparison: ETA, based on its highest coating efficiency on TiO<sub>2</sub> surfaces (Fig. S5b†), and GPDMEs that we used for TiO<sub>2</sub> nanostructure functionalization (Fig. 4c) and OTW measurements (Fig. 5). For SiO<sub>2</sub> substrates, which are functionalized under the same conditions as TiO<sub>2</sub>, both ETA and GPDMEs coatings show ~30% higher functionalization density than on TiO<sub>2</sub>. However, the coating efficiencies of TiO<sub>2</sub> are sufficient to perform single molecule OTW experiments (Fig. 5b,c). If higher coating density is required, TiO<sub>2</sub> substrates can be treated with extended O<sub>2</sub> plasma-treatment time to increase the density of surface hydroxyl groups.<sup>20</sup>

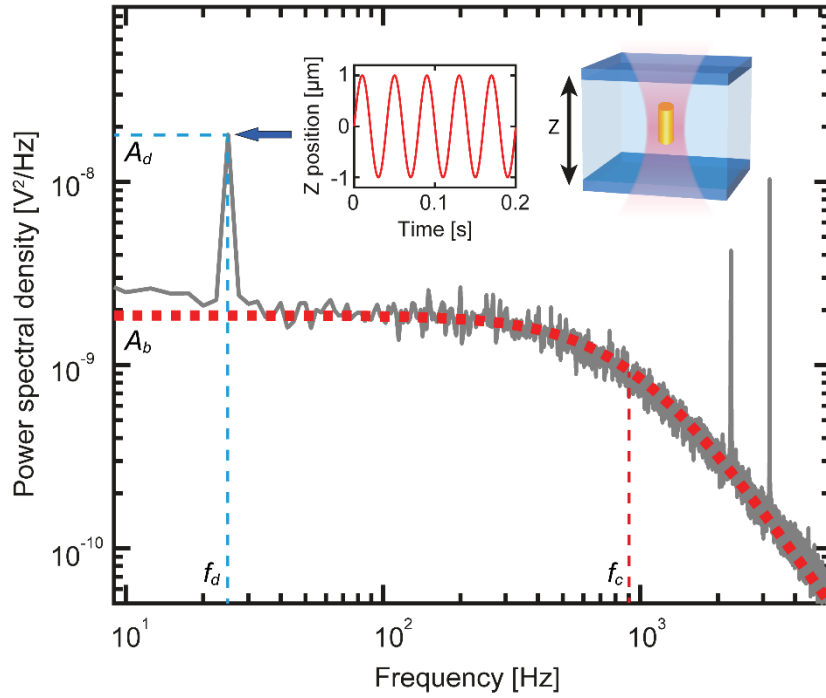


**Fig. S6.** DLS measurements of single-crystal  $\text{TiO}_2$  nanocylinder aggregation in relation to surface coatings and buffer conditions. In the DLS graphs, each curve is an average of 10 measurements with a duration of 10 s each, with 2 min between successive curves (see legend at bottom of figure). Each green shaded box within the panels displays the range of nanocylinder sizes measured previously in SEM (left edge: diameter, right edge: height). Top-left corner denotes the individual test conditions, which are surface coating (1<sup>st</sup> row) and buffer solution (2<sup>nd</sup> row). **(a-d)** Results for non-coated nanocylinders dispersed in **(a)** DI water, **(b)** DI water with 2% (m/v) BSA (New England Biolabs, UK), **(c)** PBS buffer (pH 7.4), and **(d)** PBS buffer (pH 7.4) with 2% BSA. **(e-g)** DLS data for PEGylated nanocylinders in **(e)** DI water, and in PBS buffer (pH 7.4) after bioconjugation with **(f)** biotin and **(g)** DNA. **(h)** Result for GPDMS-coated nanocylinders with bound streptavidin

in PBS buffer (pH 7.4): this condition is used for the presented single-molecule OTW experiments (**Fig. 5**). The SEM-measured nanocylinder dimensions are as follows where D (H) denotes diameters (heights): **(a,b,d)** D: ~110 nm, H: ~430 nm; **(c,e)** D: ~195 nm, H: ~585 nm; **(f)** D: ~255 nm, H: ~625 nm; **(g)** D: ~290 nm, H: ~460 nm; **(h)** D: ~105 nm, H: ~505 nm.

### Measurements and analysis of DLS data

We probe the aggregation of cleaved, isolated single-crystal TiO<sub>2</sub> nanocylinders with different surface coatings and buffer solutions via DLS (Zetasizer Nano ZS, Malvern, UK). We compare the degree of nanocylinder aggregations by characterizing the nanocylinder size distributions with 173° backscattering angle at 25 °C. To achieve monodispersed nanocylinders in aqueous solution, we vortex the nanocylinder solutions for 1 min before each measurement. However, for the nanocylinders in **Fig. S6a†** and **Fig. S6b†**, vortexing is insufficient to obtain monodispersity. For these samples, we sonicate the solutions for 10 min before measurements. We attribute the mismatch between nanocylinder dimensions (green boxes) based on SEM image analysis and size measurements via DLS to the highly scattering nature of TiO<sub>2</sub> and non-spherical shape of the nanocylinders. Besides the aggregated nanocylinder solutions (**Fig. S6a,b,d†**) which are apparent from the severe broadening of the size distributions, the monodispersed nanocylinder solutions (**Fig. S6c,e-h†**) exhibit only sedimentation of nanocylinders over time, observable by intensity decrease.



**Fig. S7.** Optical trap calibration of single-crystal TiO<sub>2</sub> nanocylinders. The power spectral density (gray curve) of a trapped TiO<sub>2</sub> nanocylinder with a Lorentzian fit (red dotted line) provides corner frequency ( $f_c$ ) and baseline amplitude ( $A_b$ ). A piezo stage drives the flow cell sinusoidally in time (with amplitude of 1  $\mu\text{m}$  and frequency of 25 Hz) along the  $z$ -axis (inset) to induce a drag force to the trapped nanocylinder. The driving frequency ( $f_d$ ) of this modulation appears as a spike in the power spectrum (blue arrow), with amplitude  $A_d$ . Analysis of the three measured values ( $A_b$ ,  $A_d$ , and  $f_c$ ) yields the three necessary parameters for the force calibration in an OTW: nanocylinder drag coefficient, PSD sensitivity, and trap stiffness.<sup>21</sup>

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